

FIG. 1A

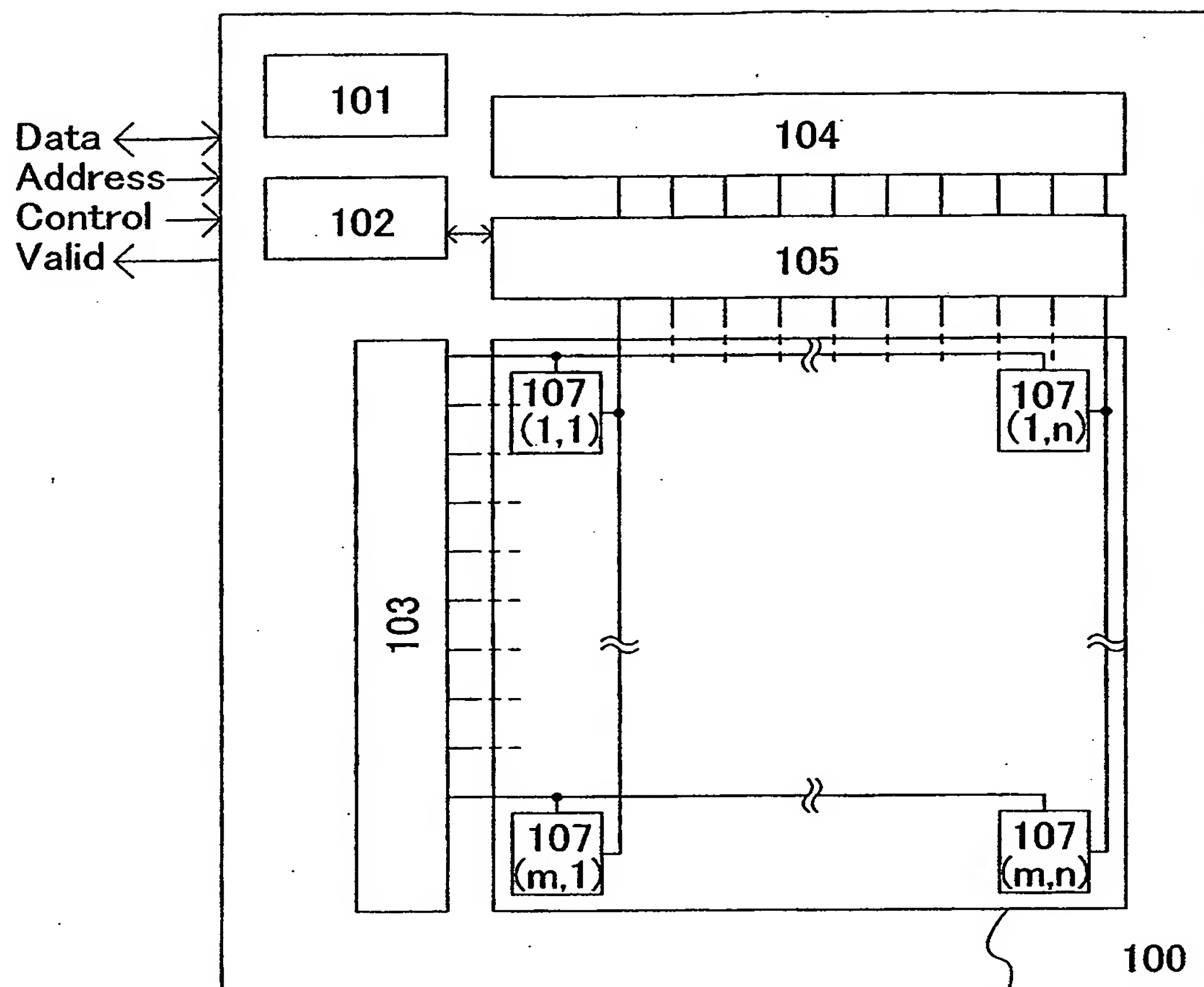


FIG. 1B

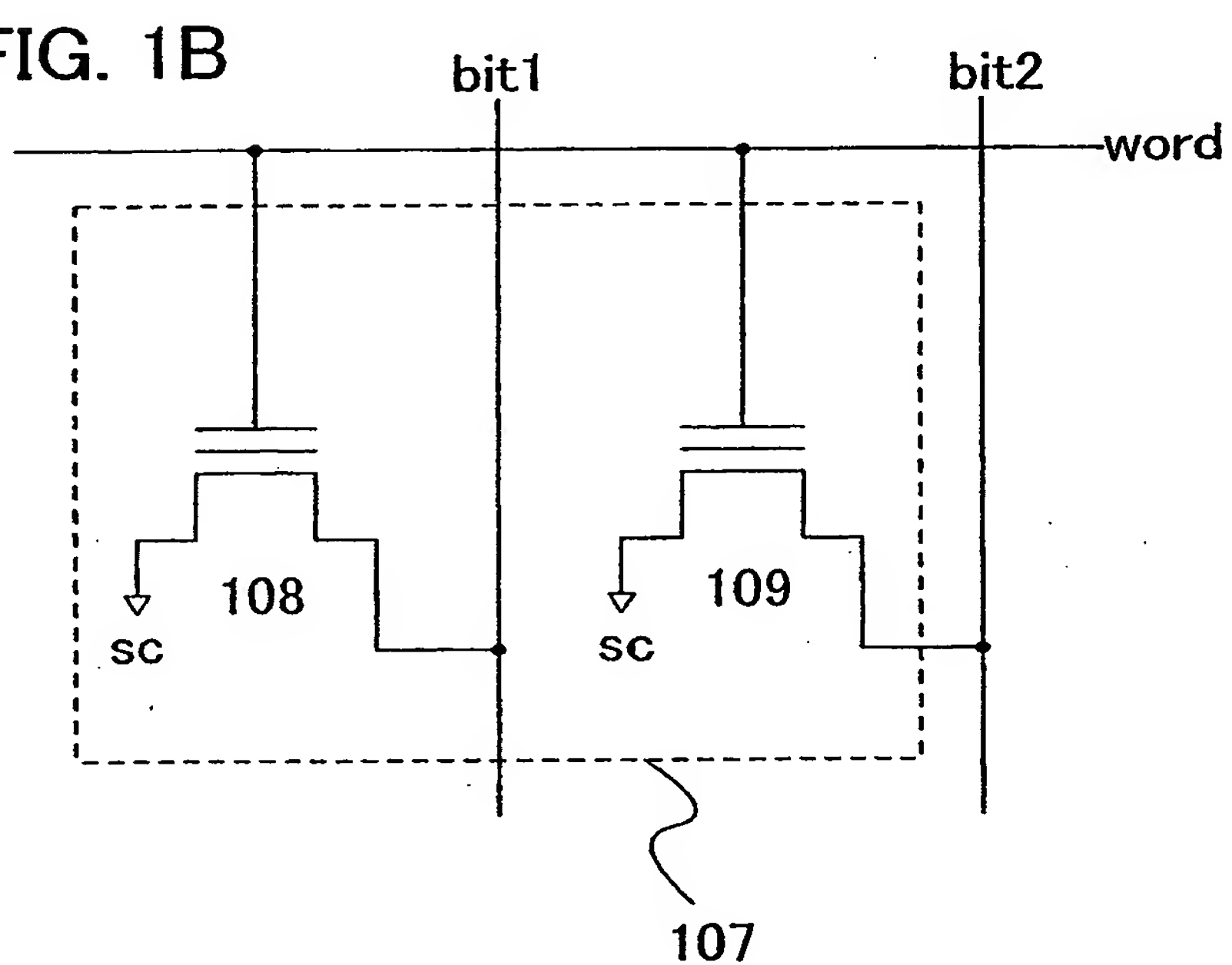


FIG. 2A

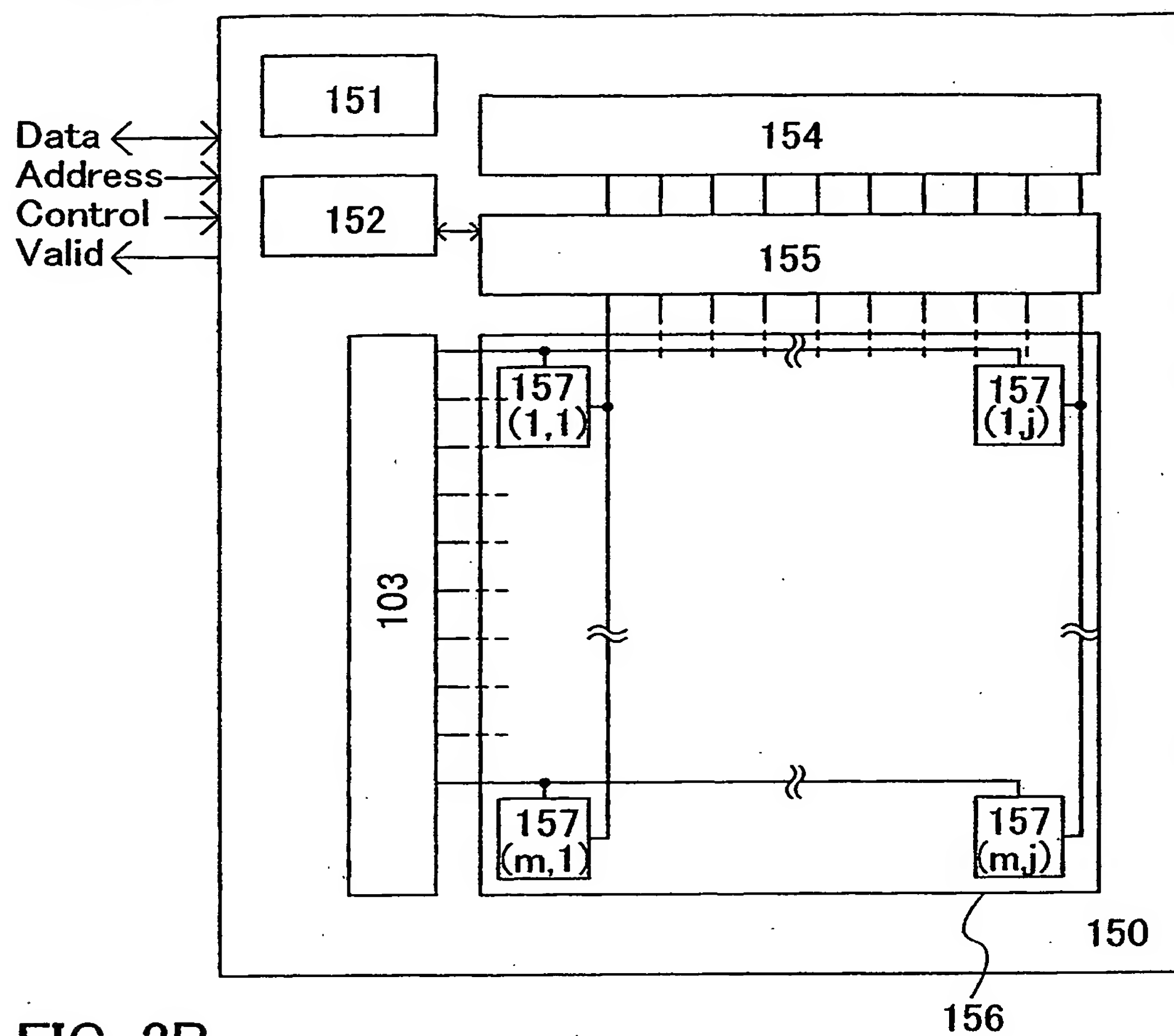


FIG. 2B

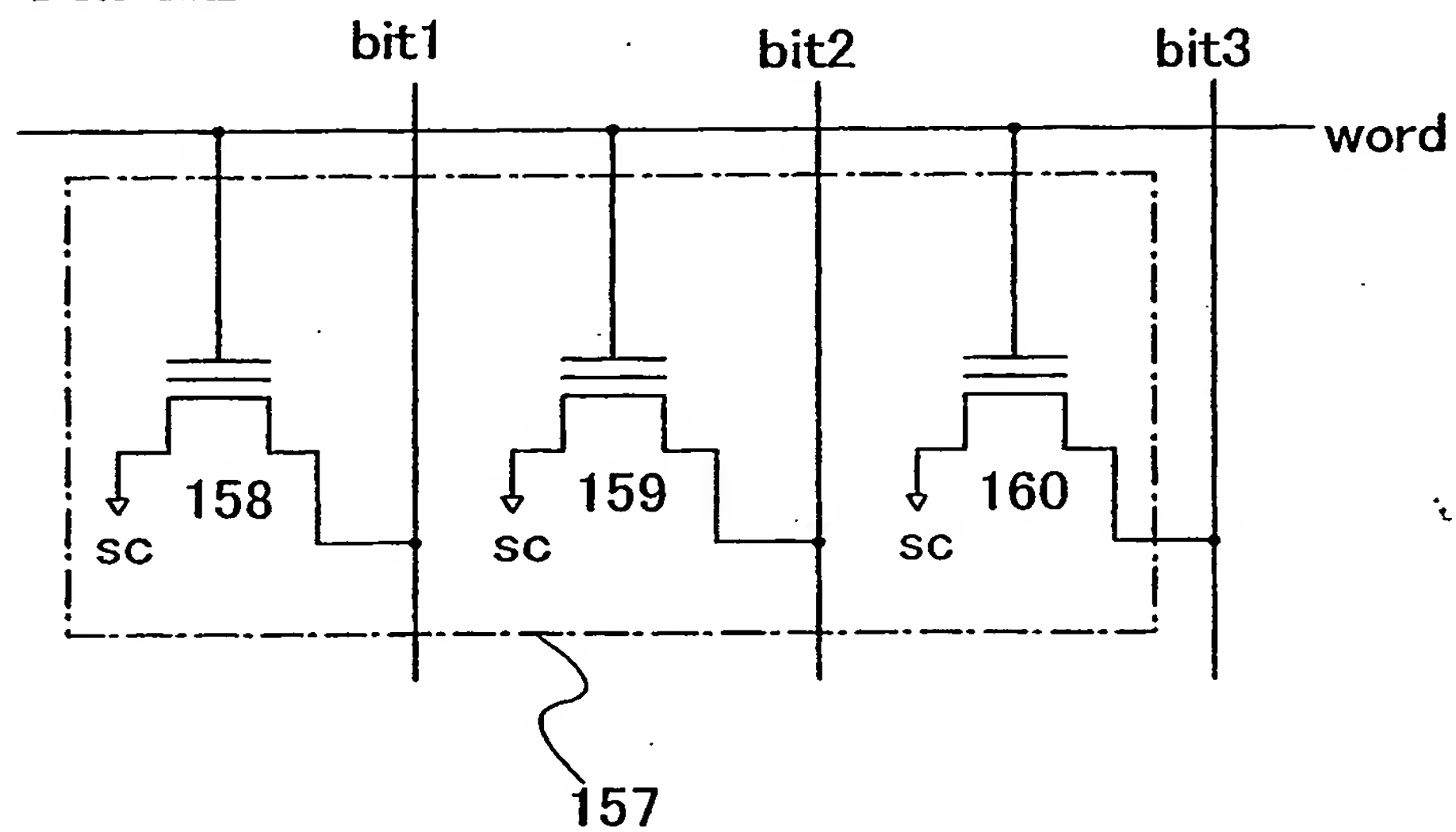


FIG. 3

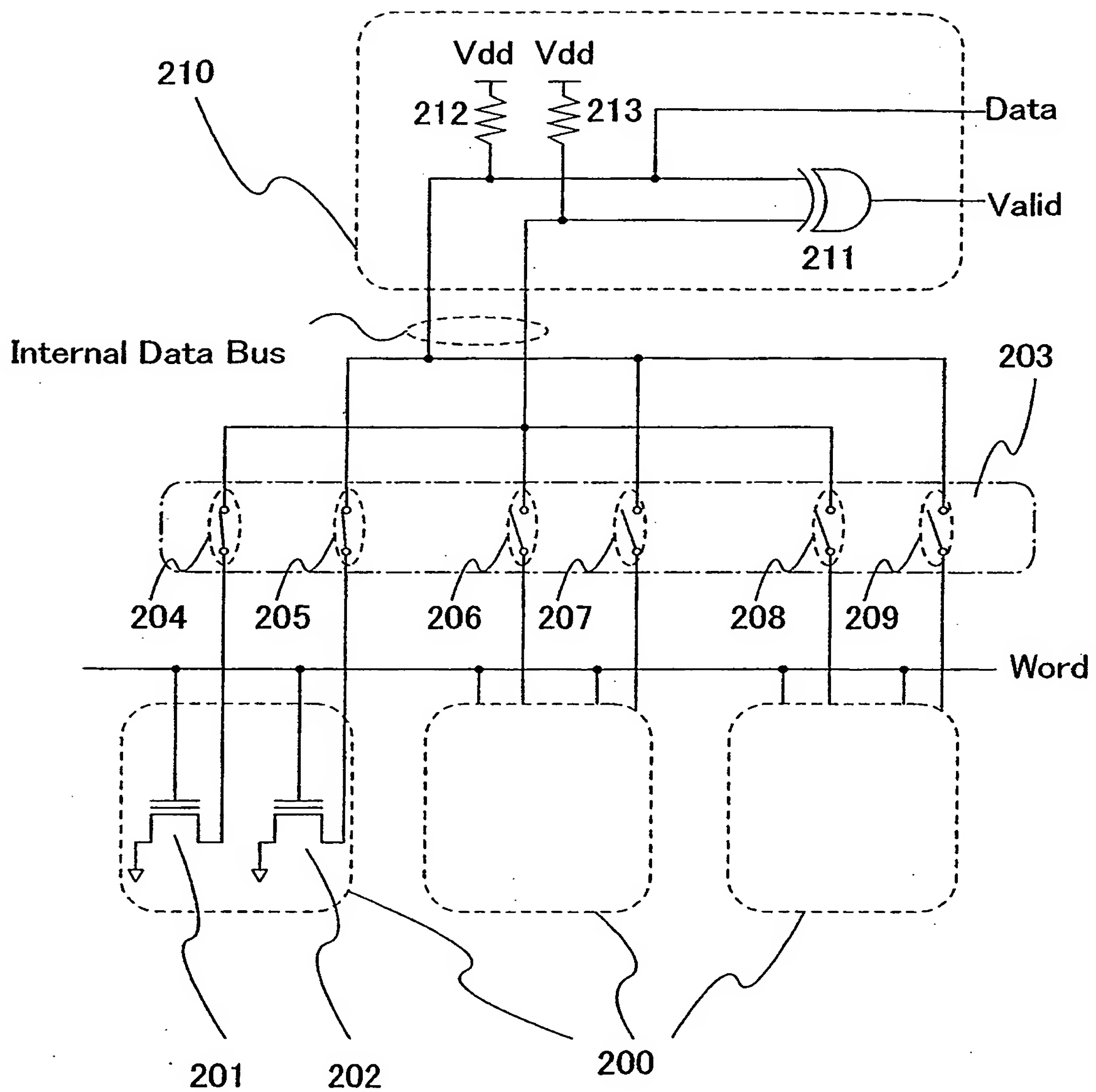


FIG. 4

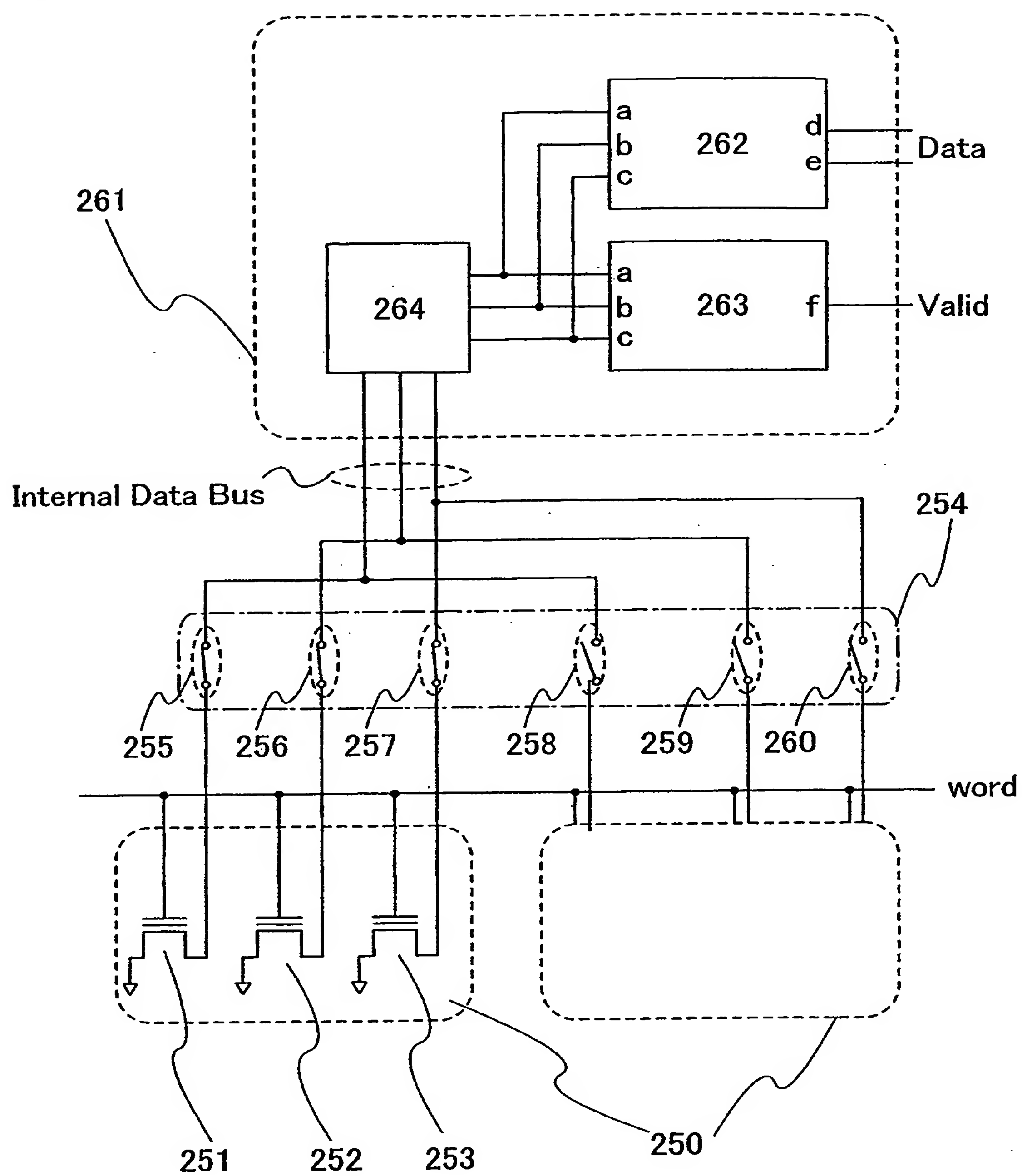
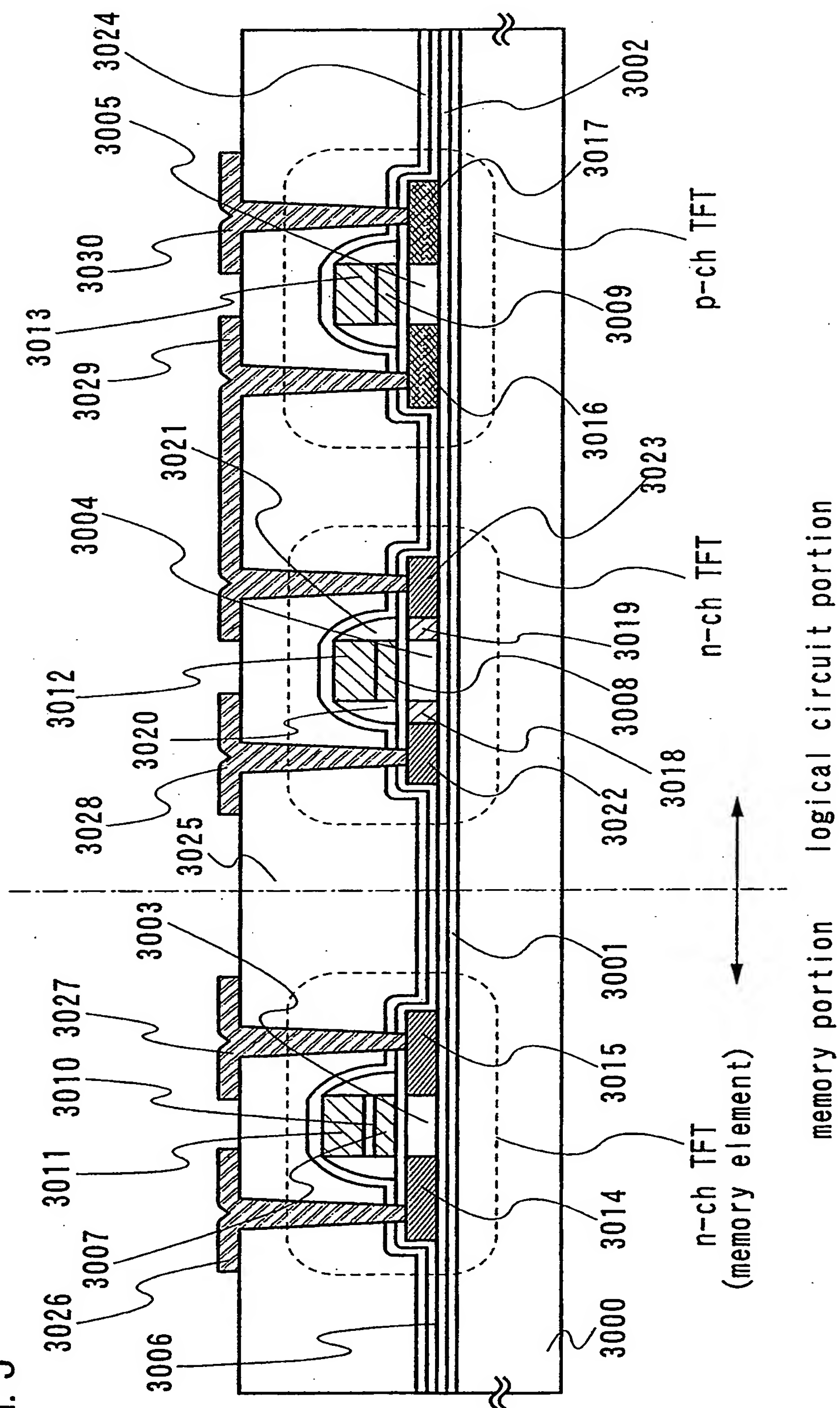


FIG. 5



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FIG. 6

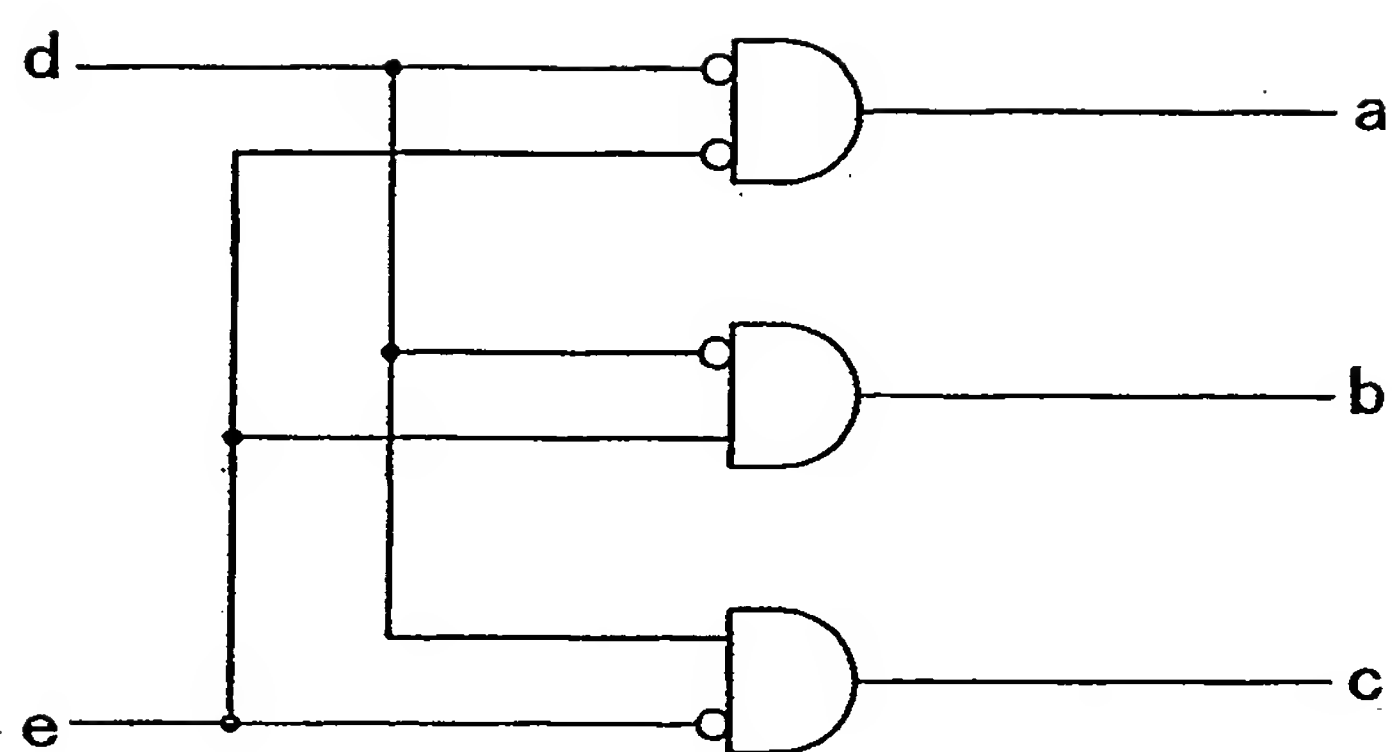
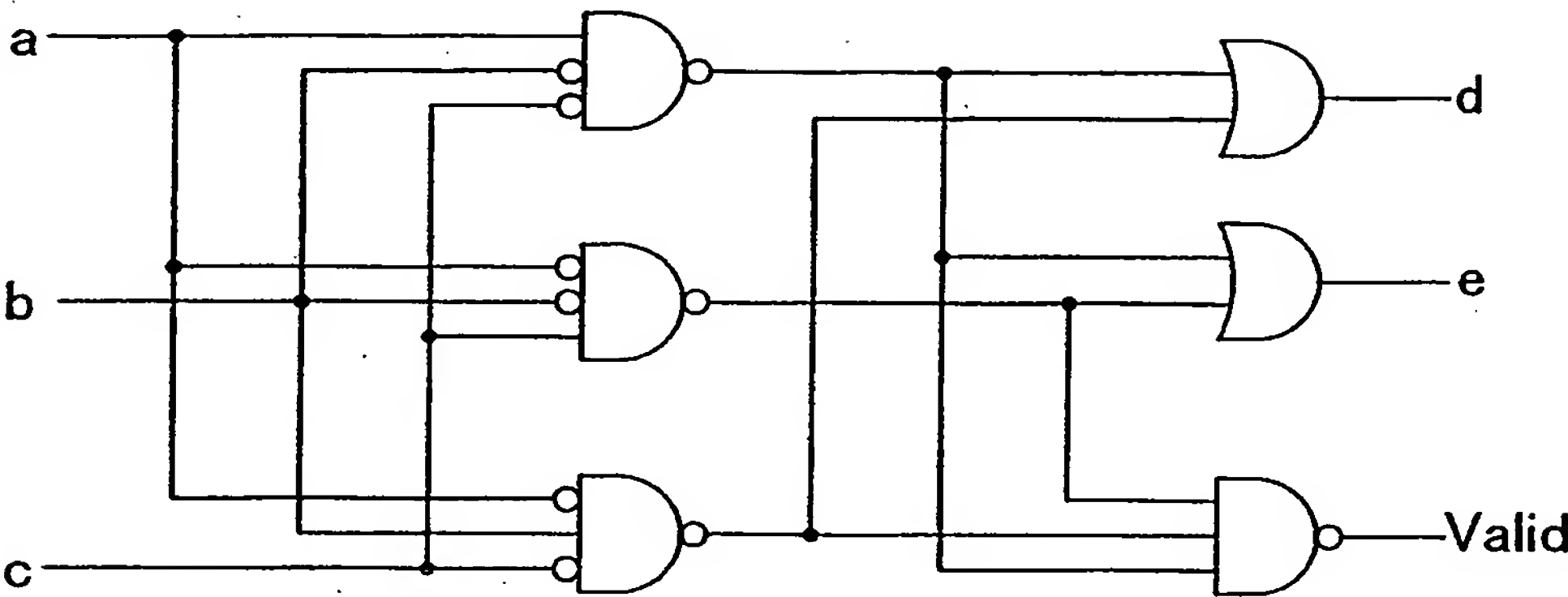
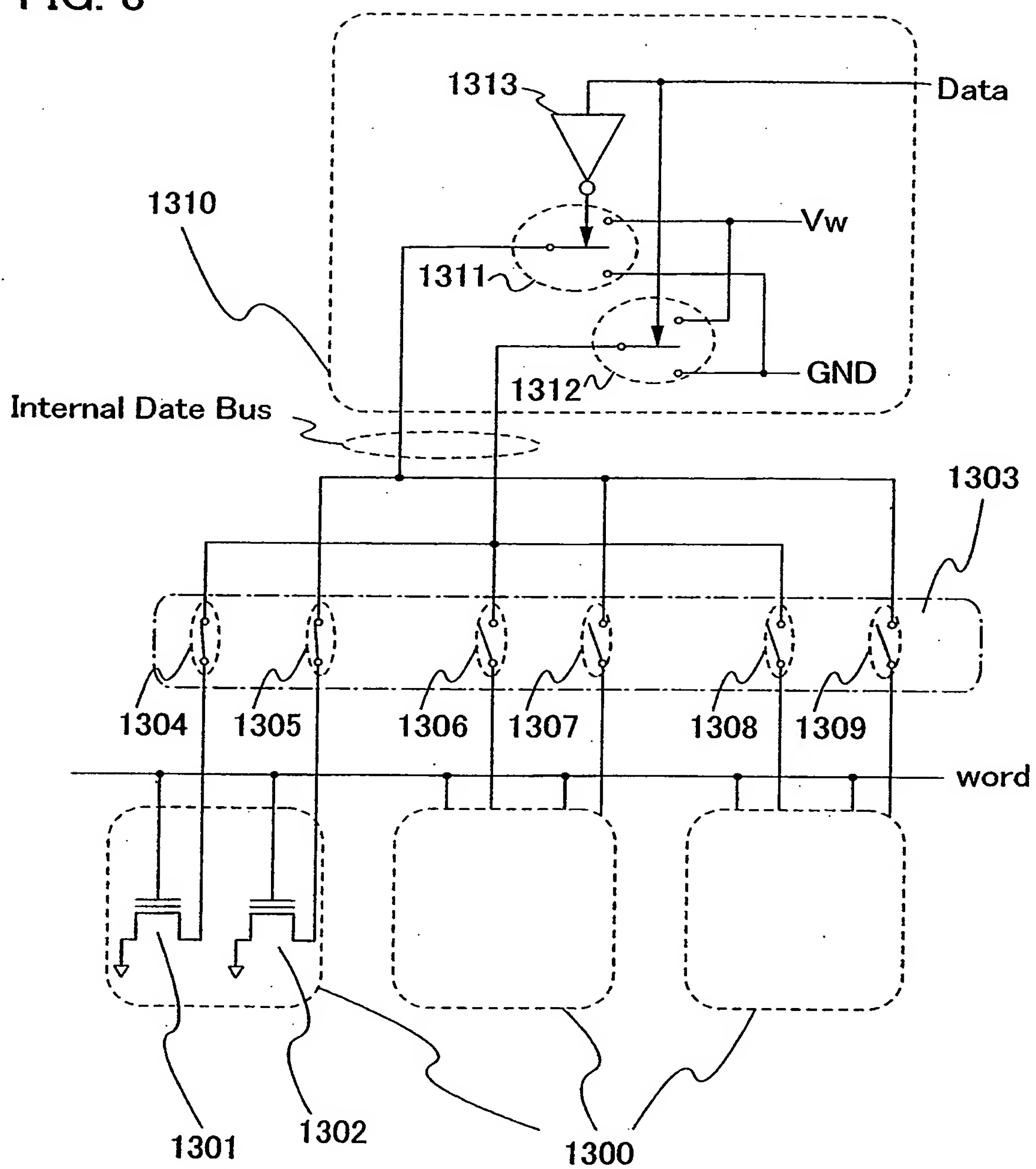


FIG. 7



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FIG. 8





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FIG. 9

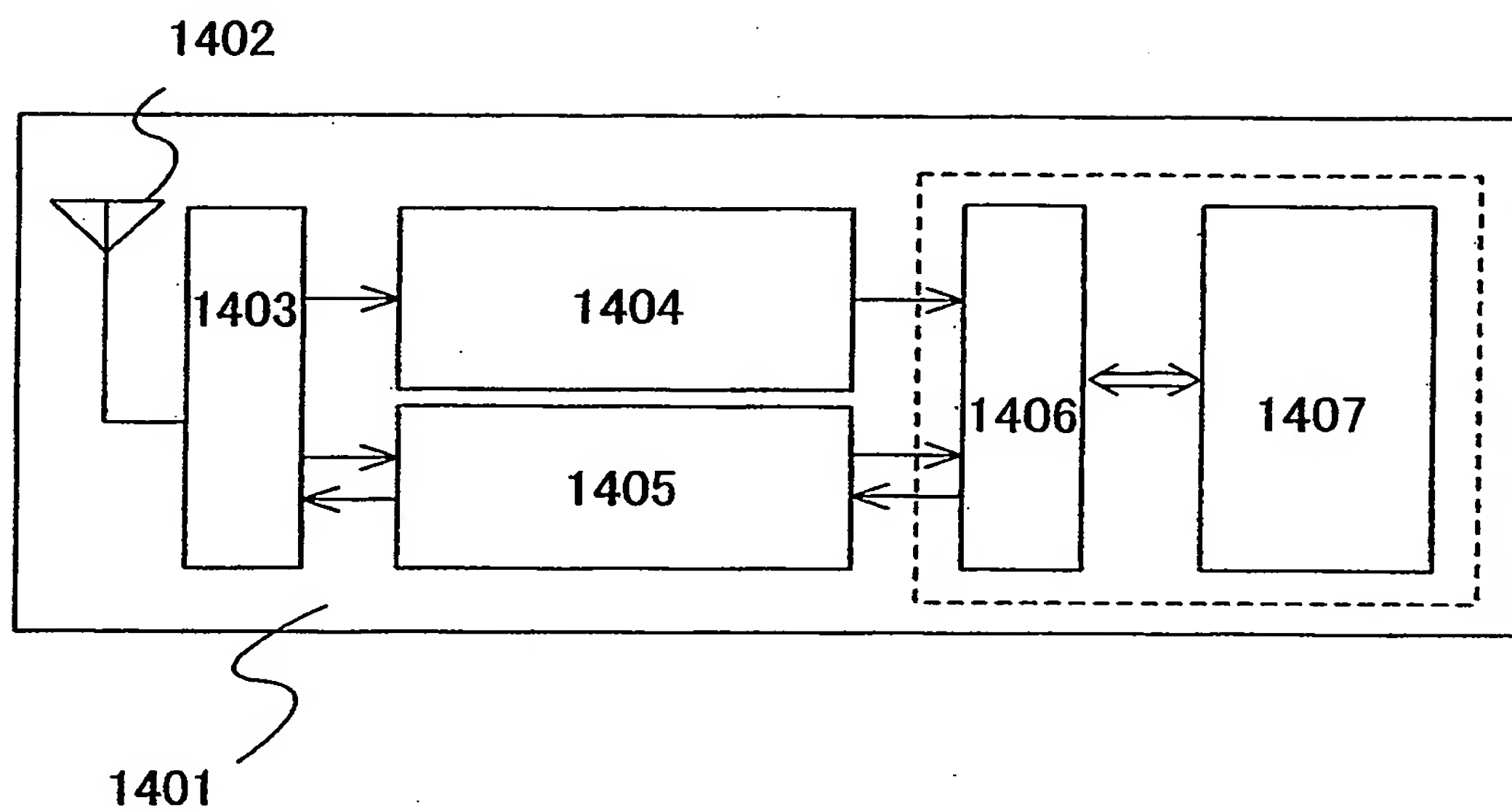


FIG. 10A

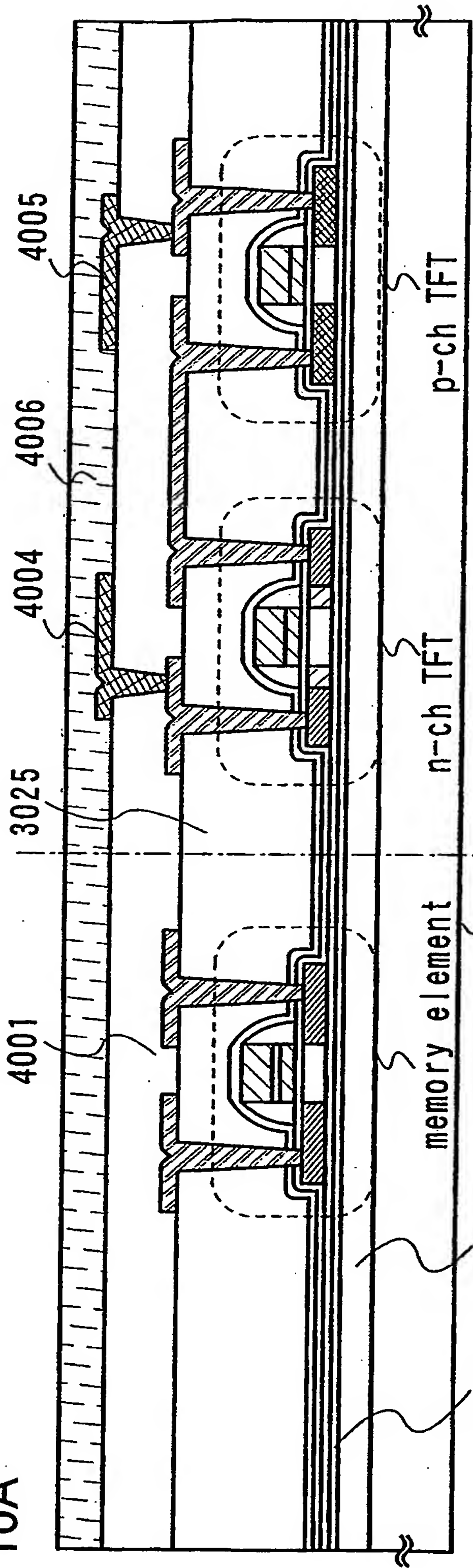


FIG. 10B

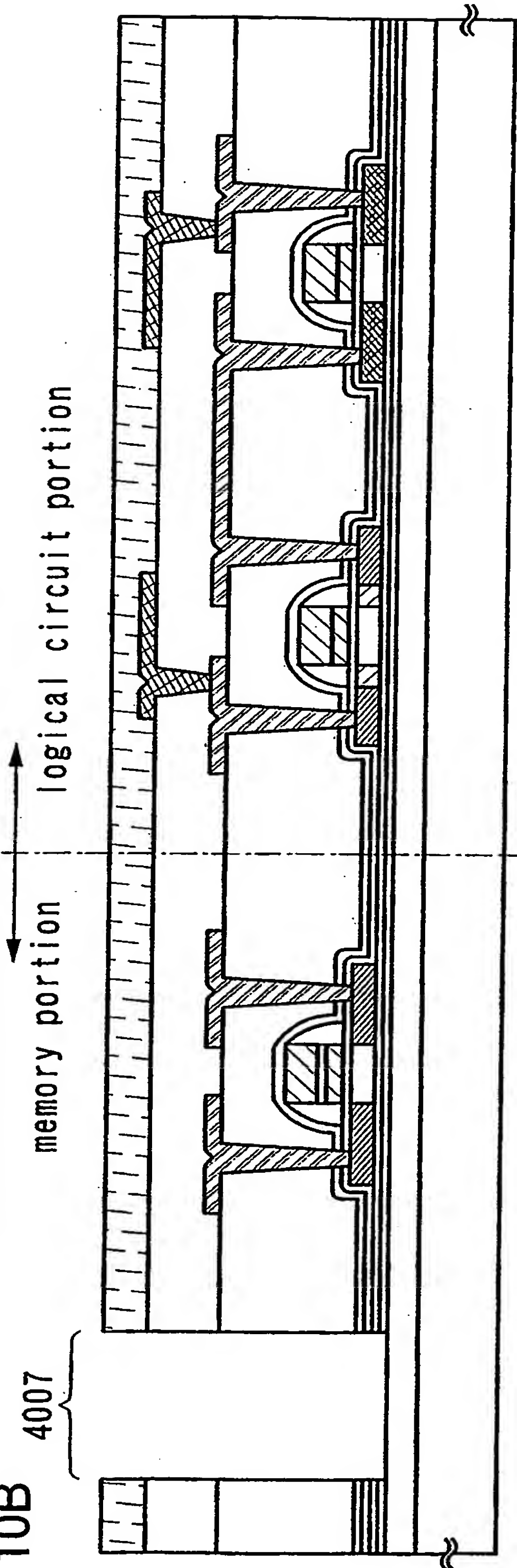


FIG. 11A

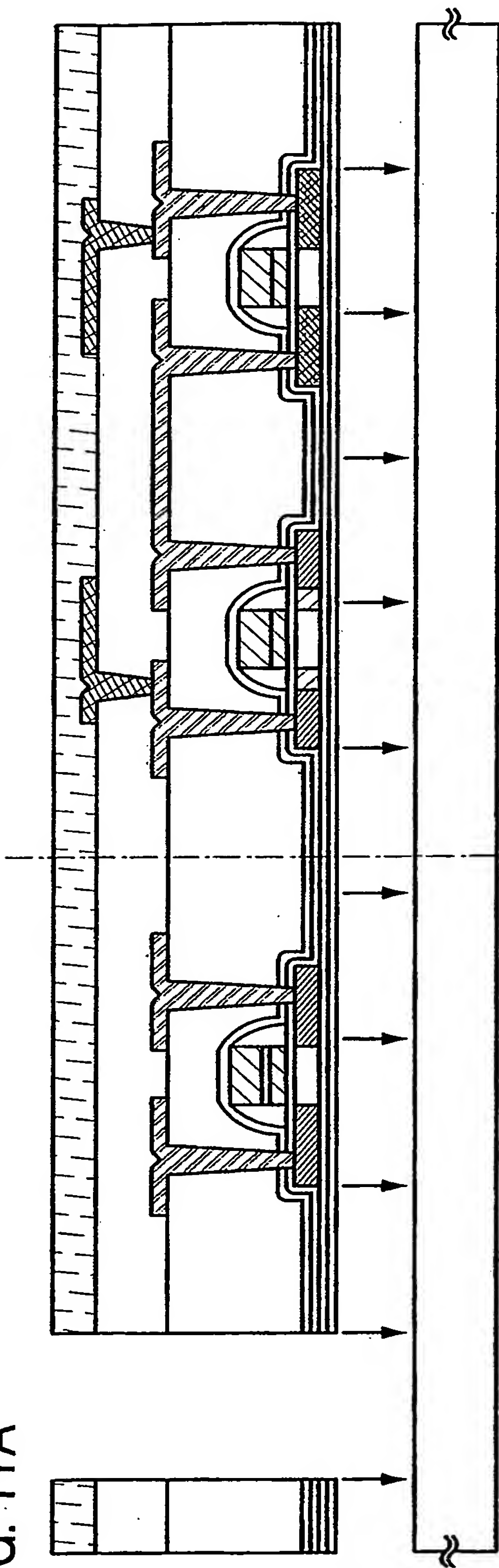
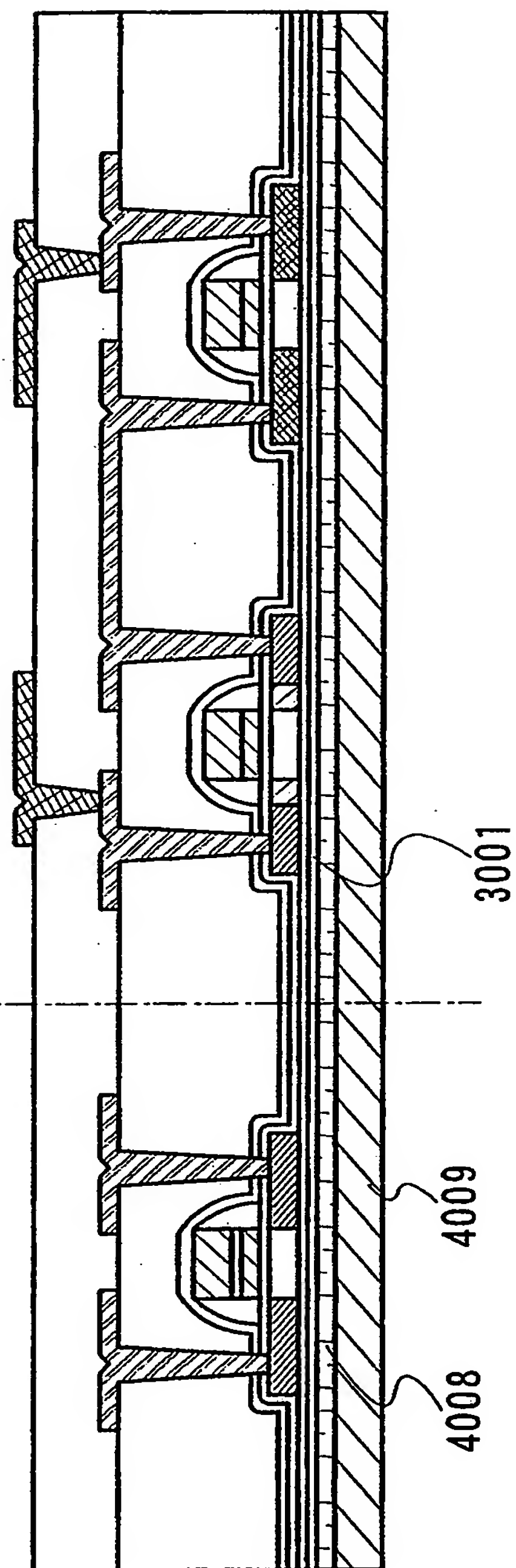


FIG. 11B



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FIG. 12A

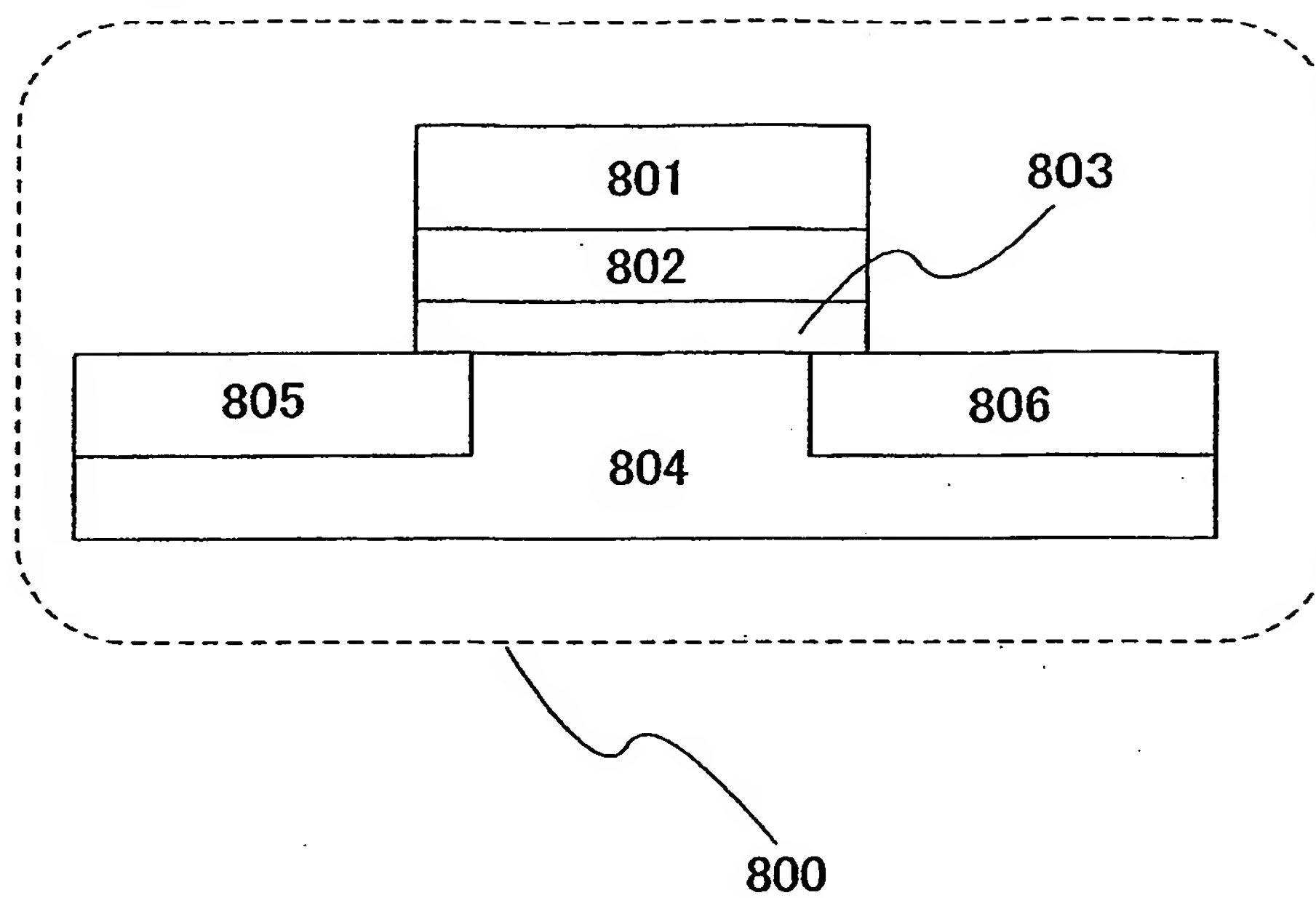


FIG. 12B

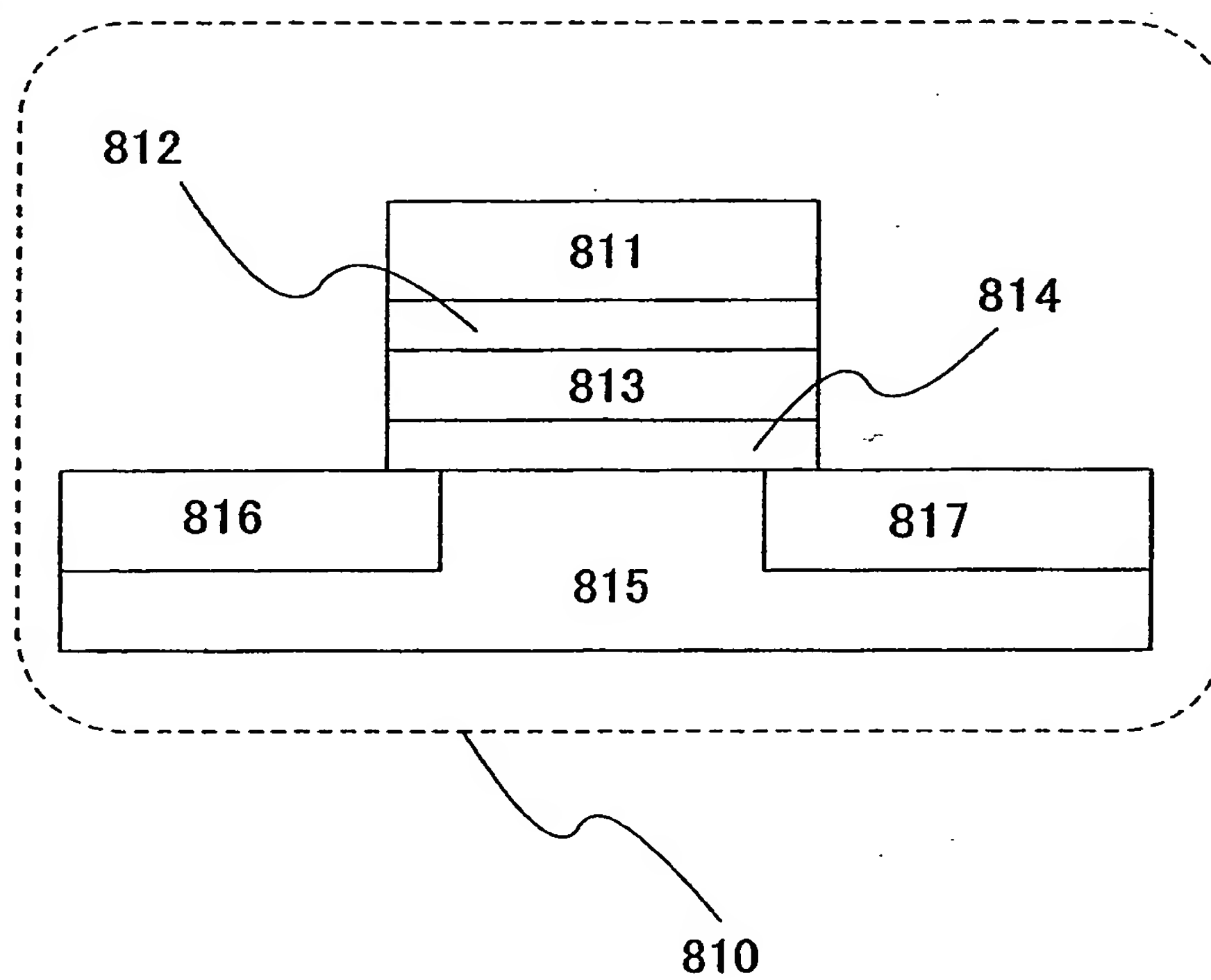


FIG. 13

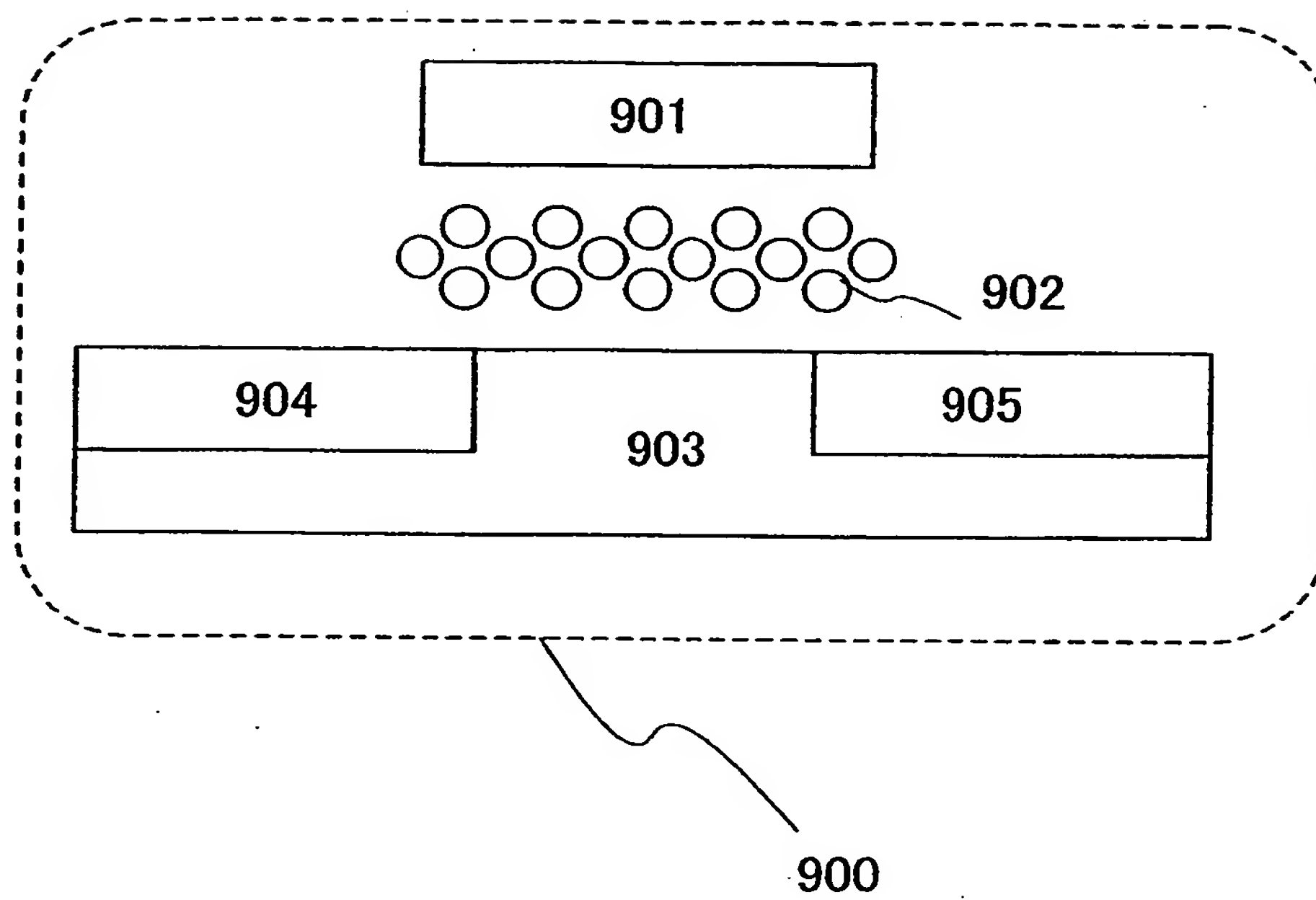


FIG. 14A

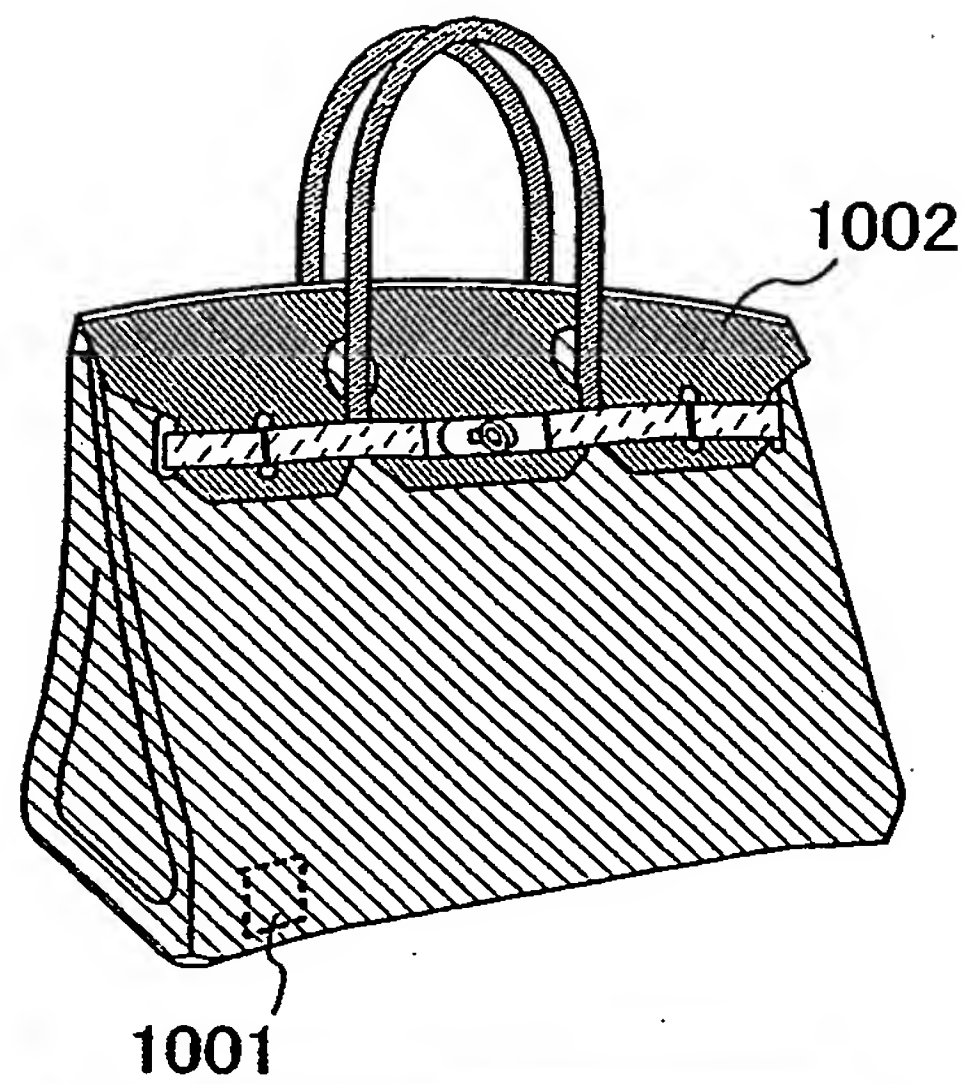


FIG. 14B

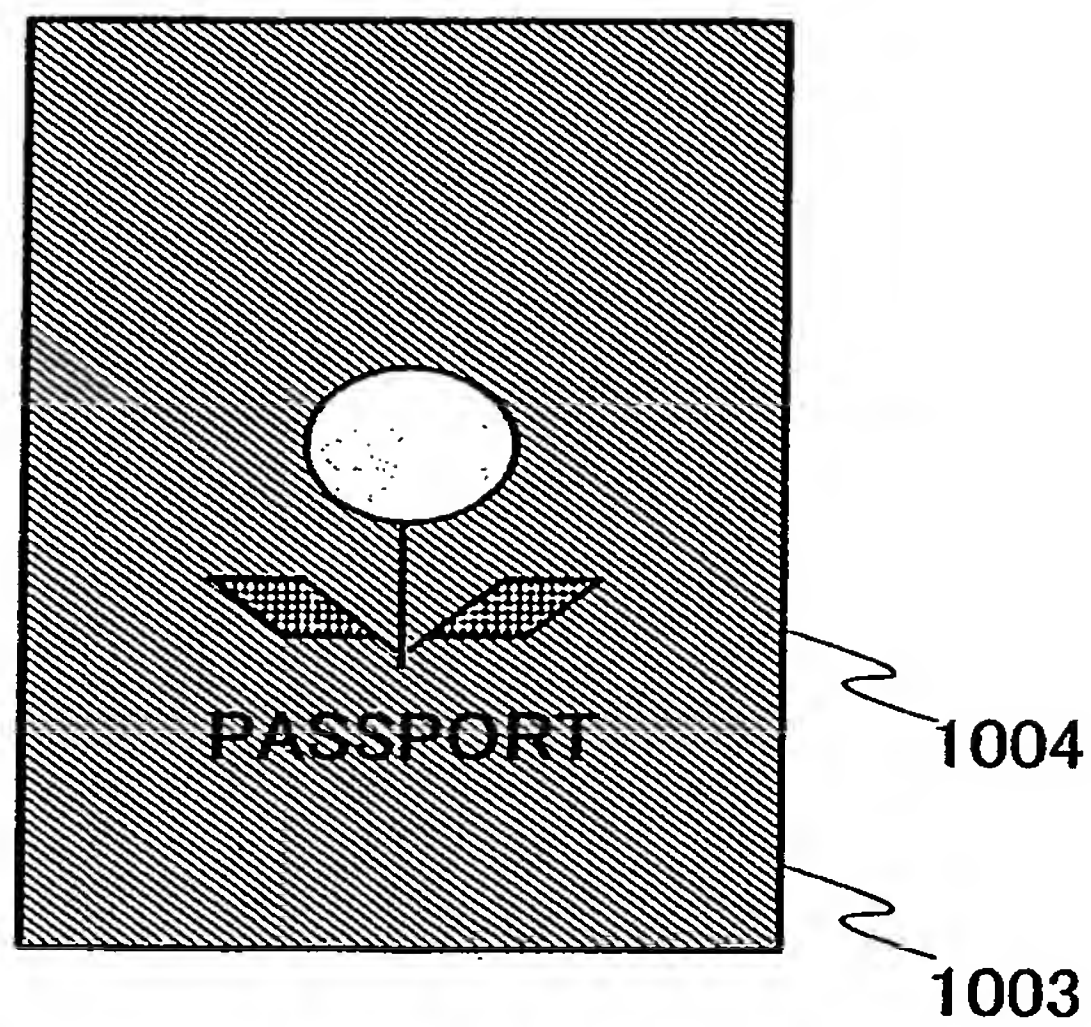


FIG. 14C

A form 1005 with the following fields:

|         |            |            |
|---------|------------|------------|
| NAME    | ○○ ○○      | YYYY/MM/DD |
| BIRTH   | ○○○○○○     |            |
| ADDRESS | ○○○○○○     |            |
| ISSUE   | YYYY/MM/DD |            |
| No.     | ○○○○○      |            |
| OTHERS  |            |            |

The form includes a large rectangular area 1006 on the right side and a dashed rectangular area 1005 at the bottom right.

FIG. 15A

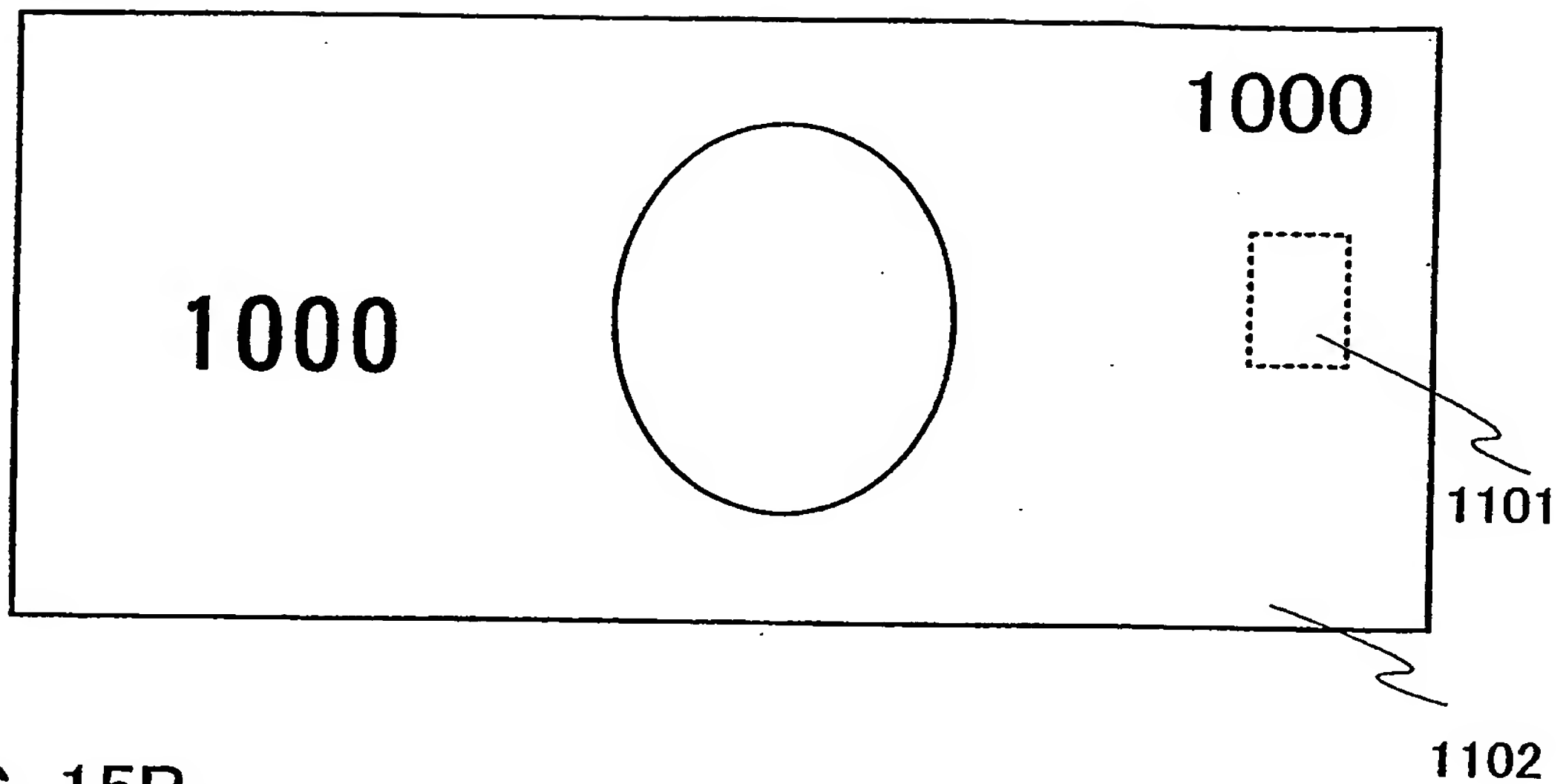


FIG. 15B

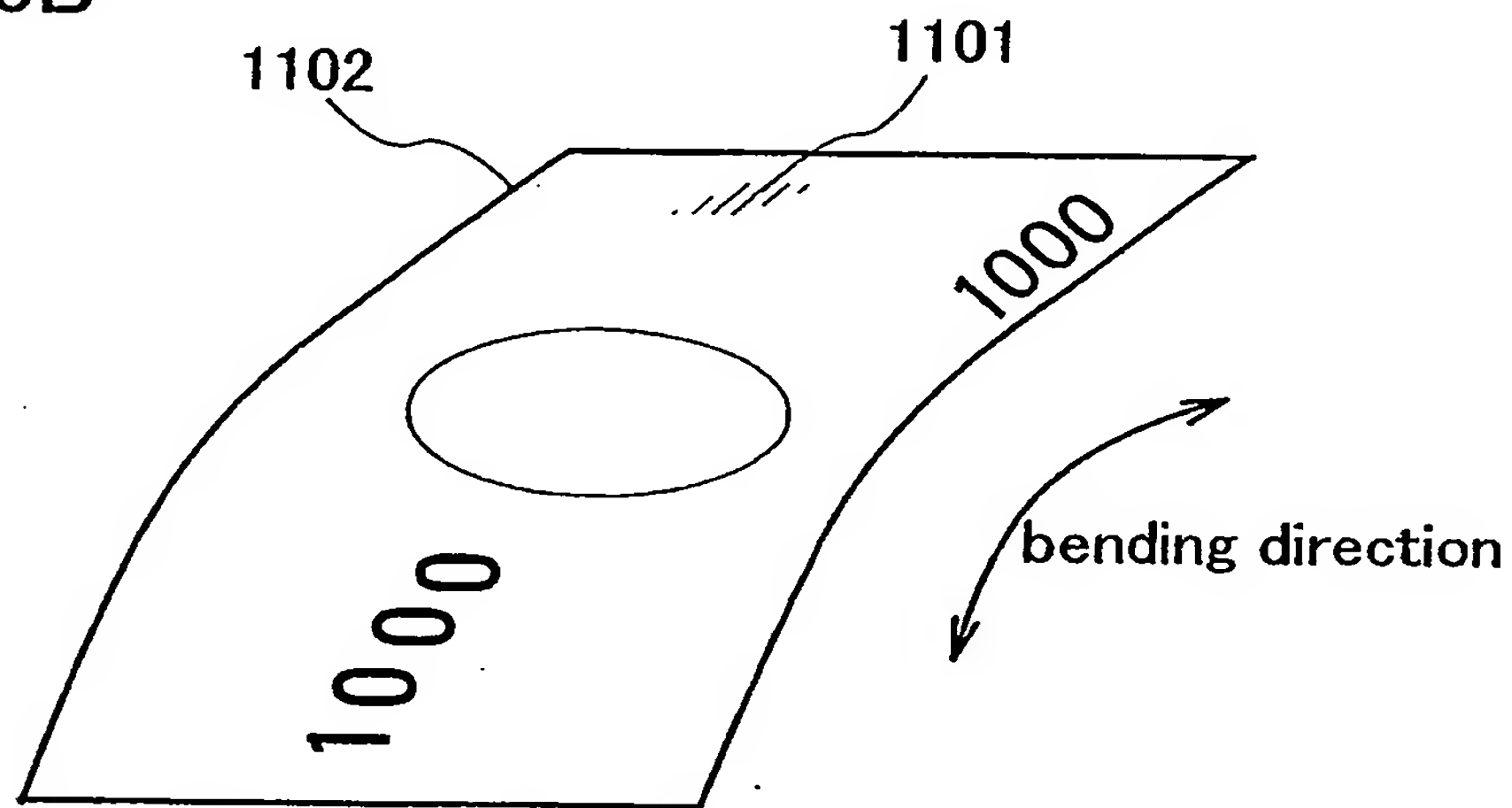


FIG. 15C

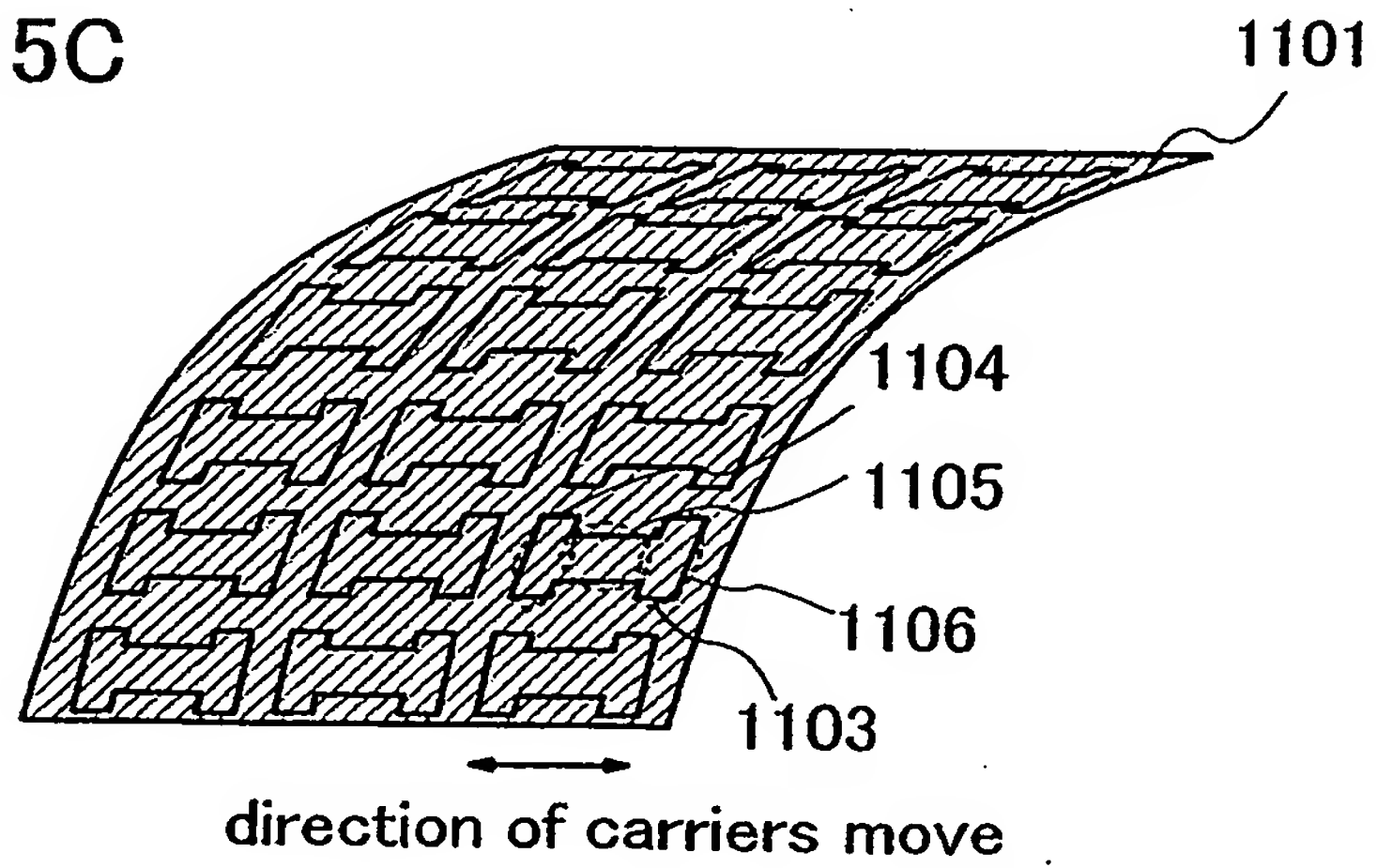


FIG. 16A

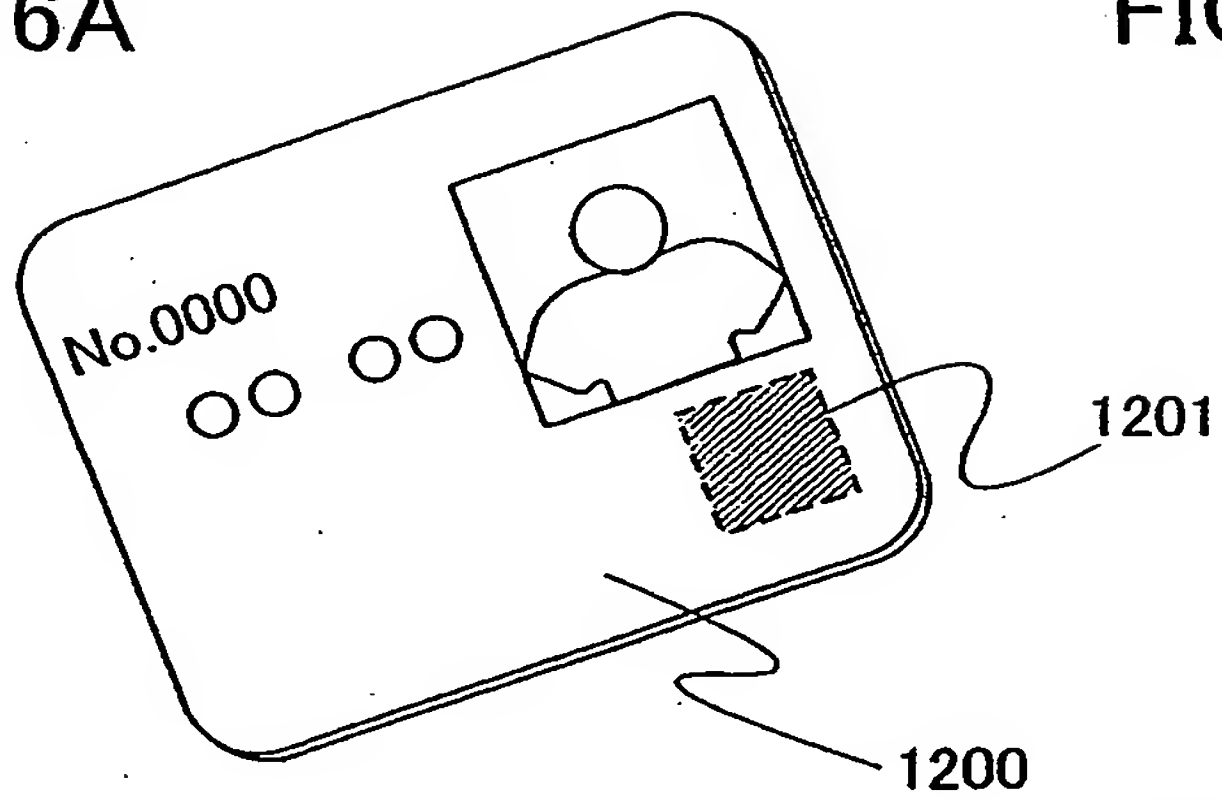


FIG. 1B

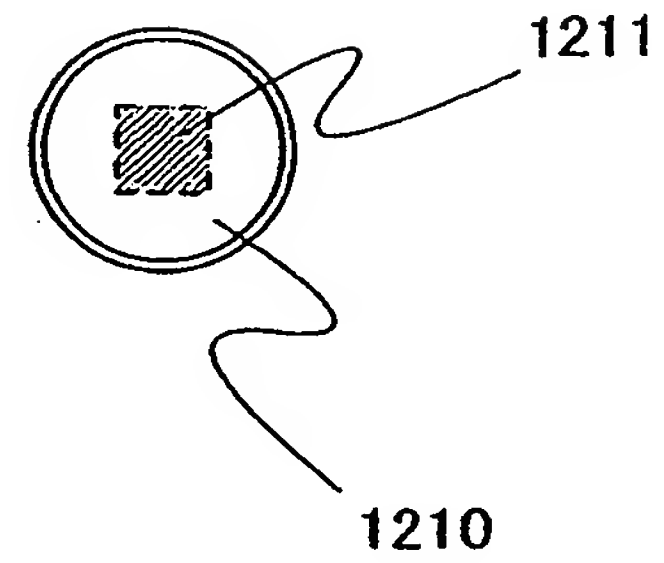


FIG. 16C

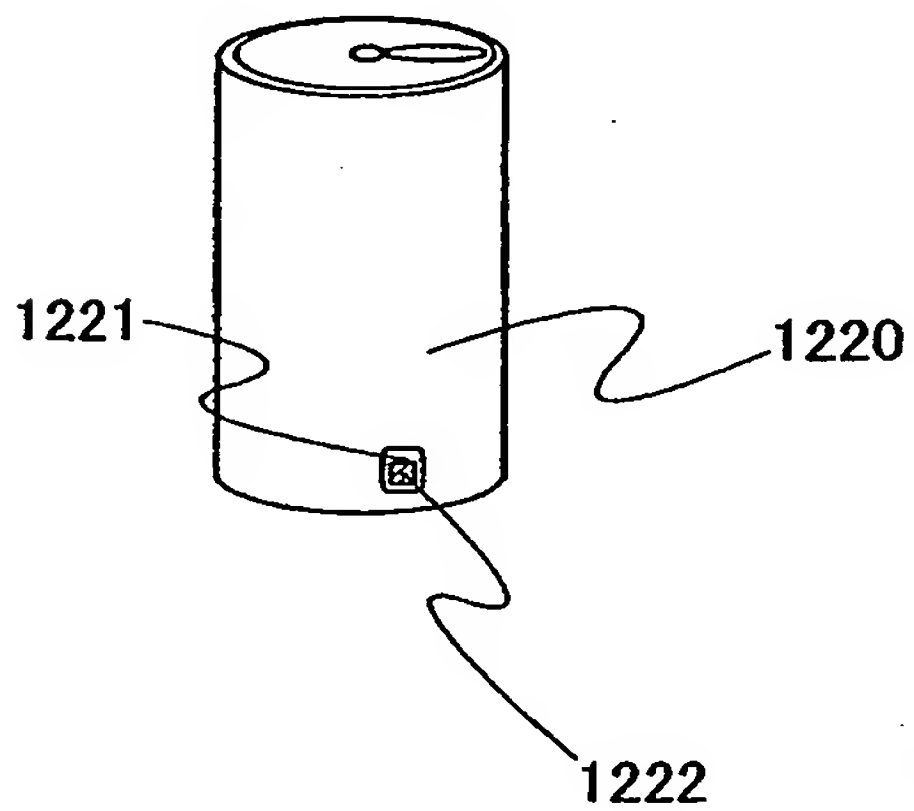


FIG. 16D

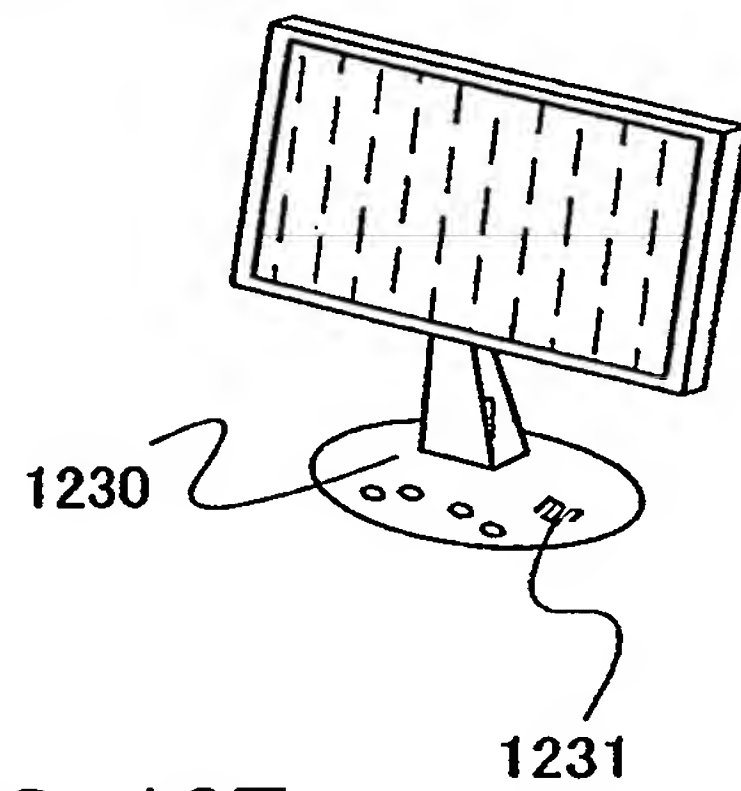


FIG. 16E

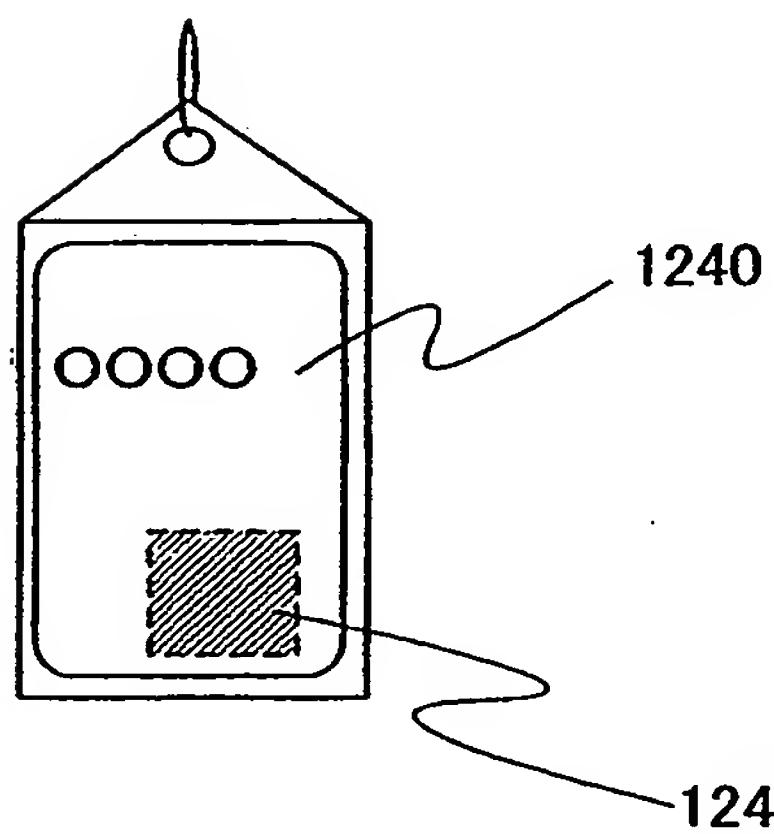


FIG. 16F

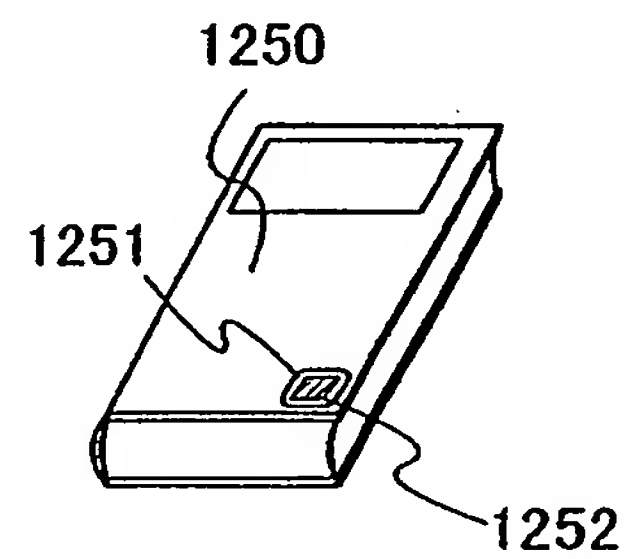


FIG. 16G

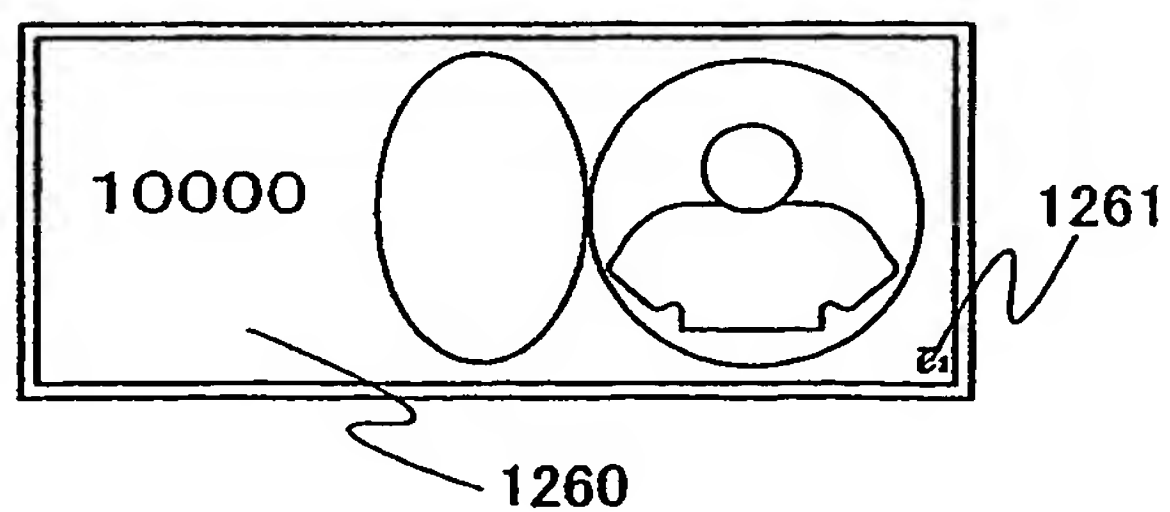


FIG. 16H

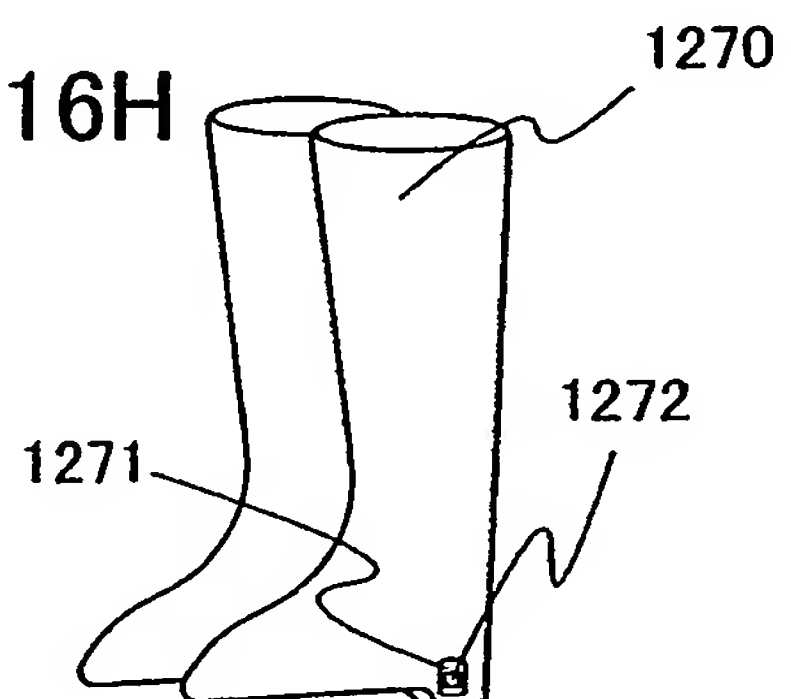




FIG. 17A

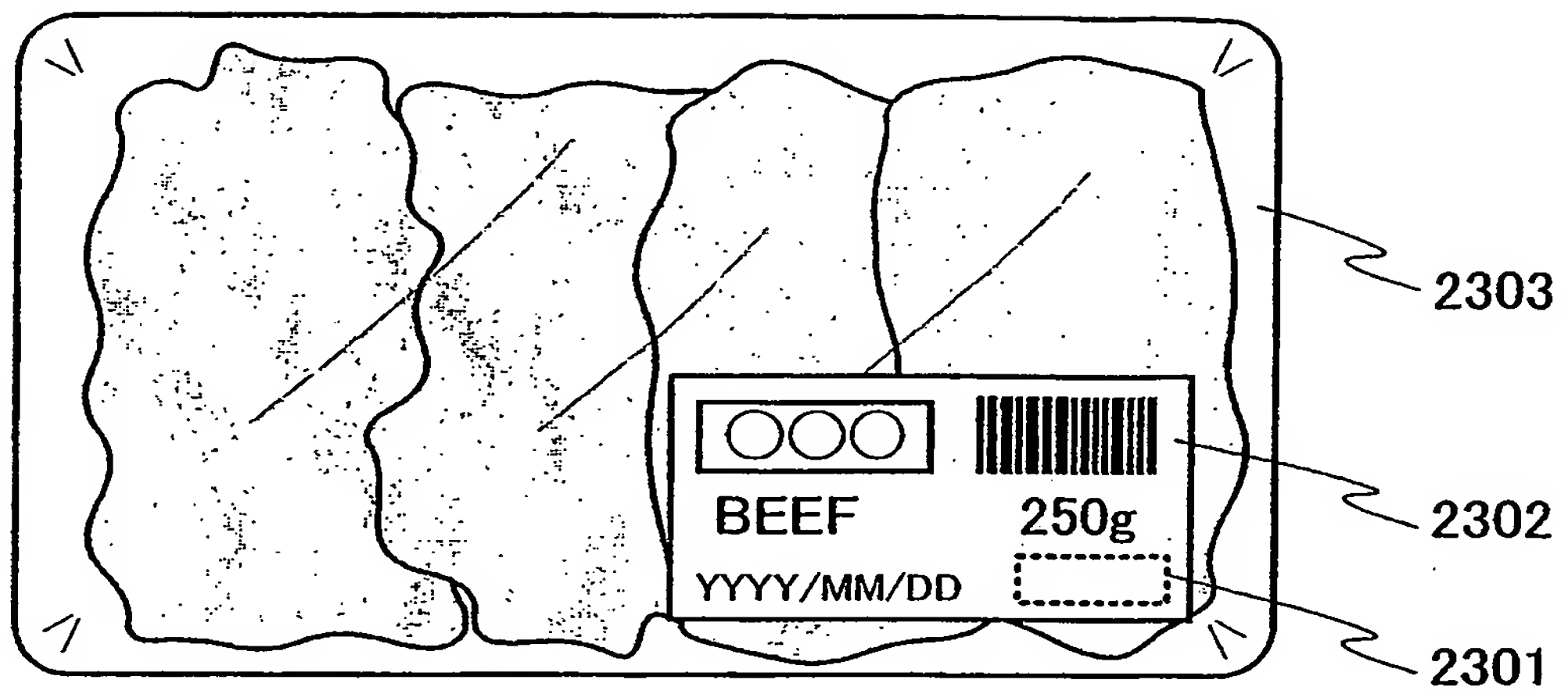


FIG. 17B

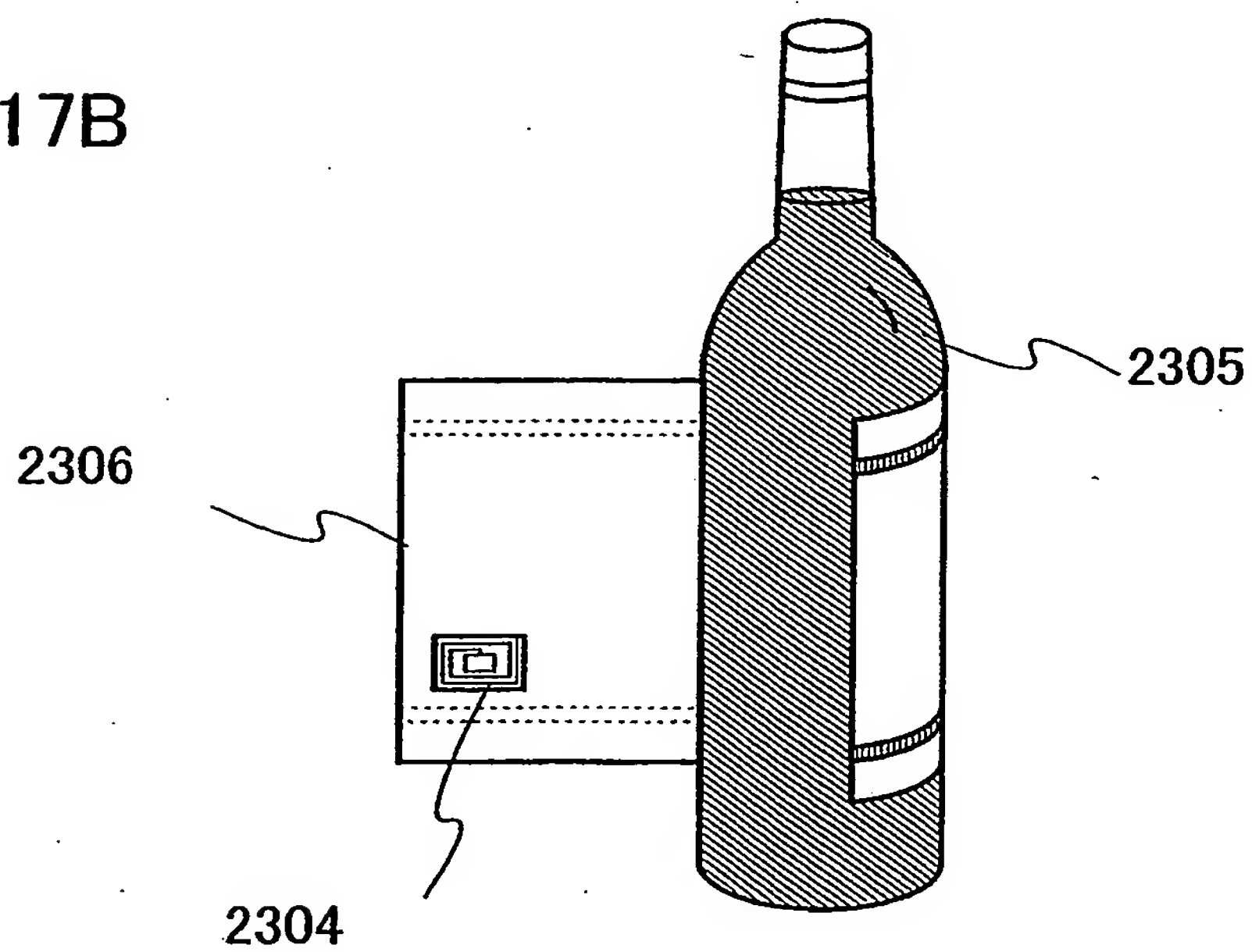
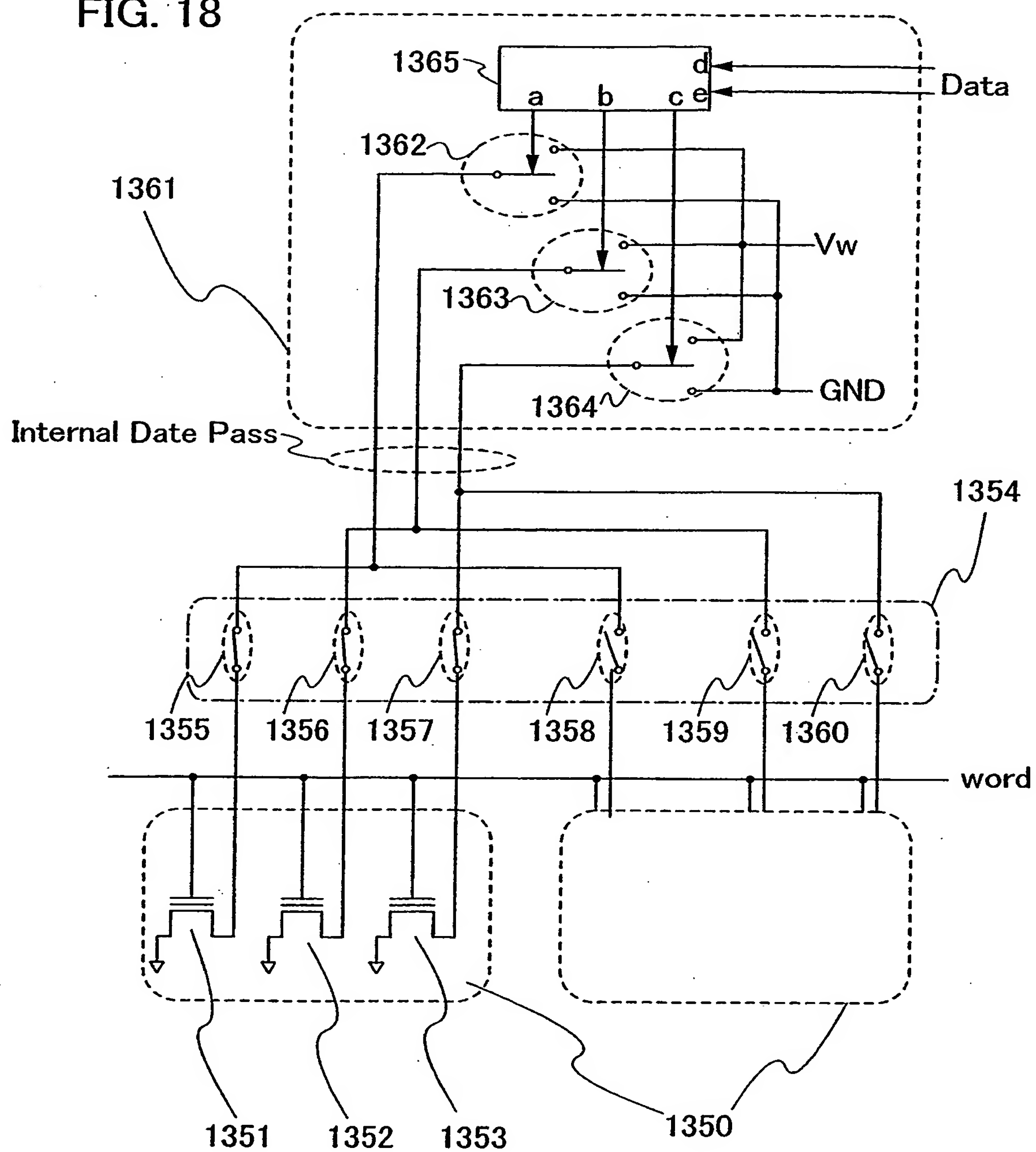


FIG. 18



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FIG. 19

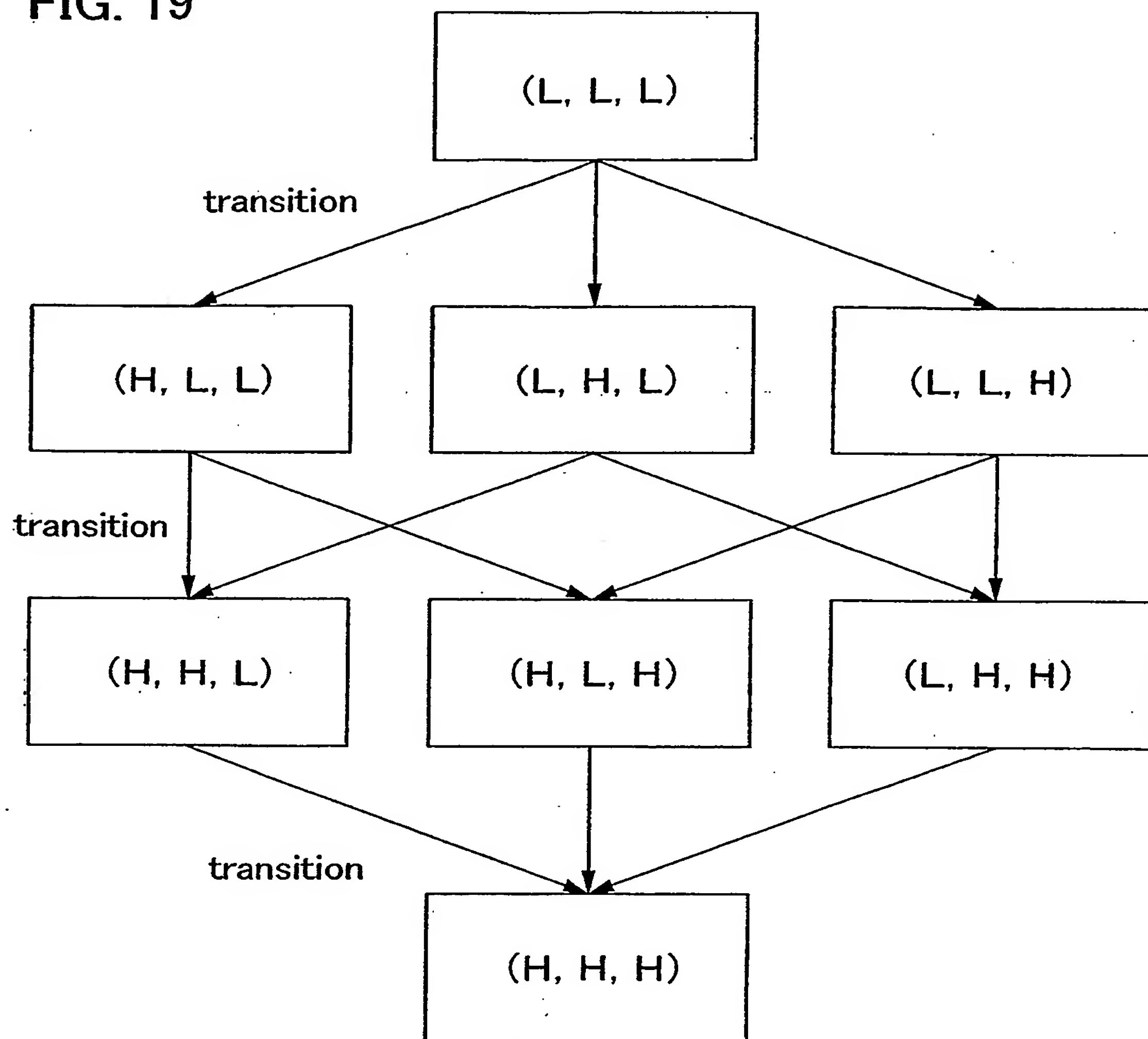


FIG. 20A

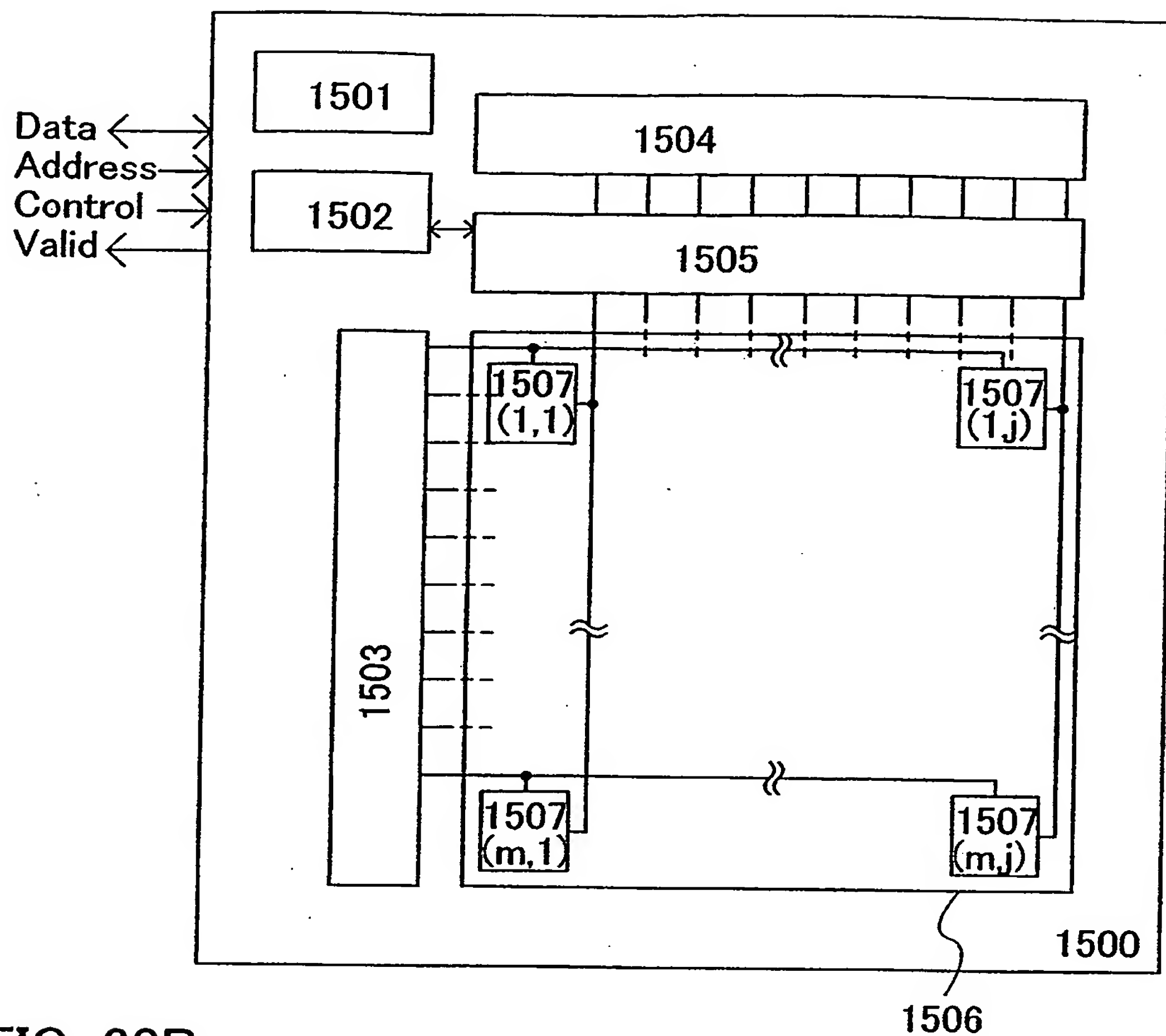


FIG. 20B

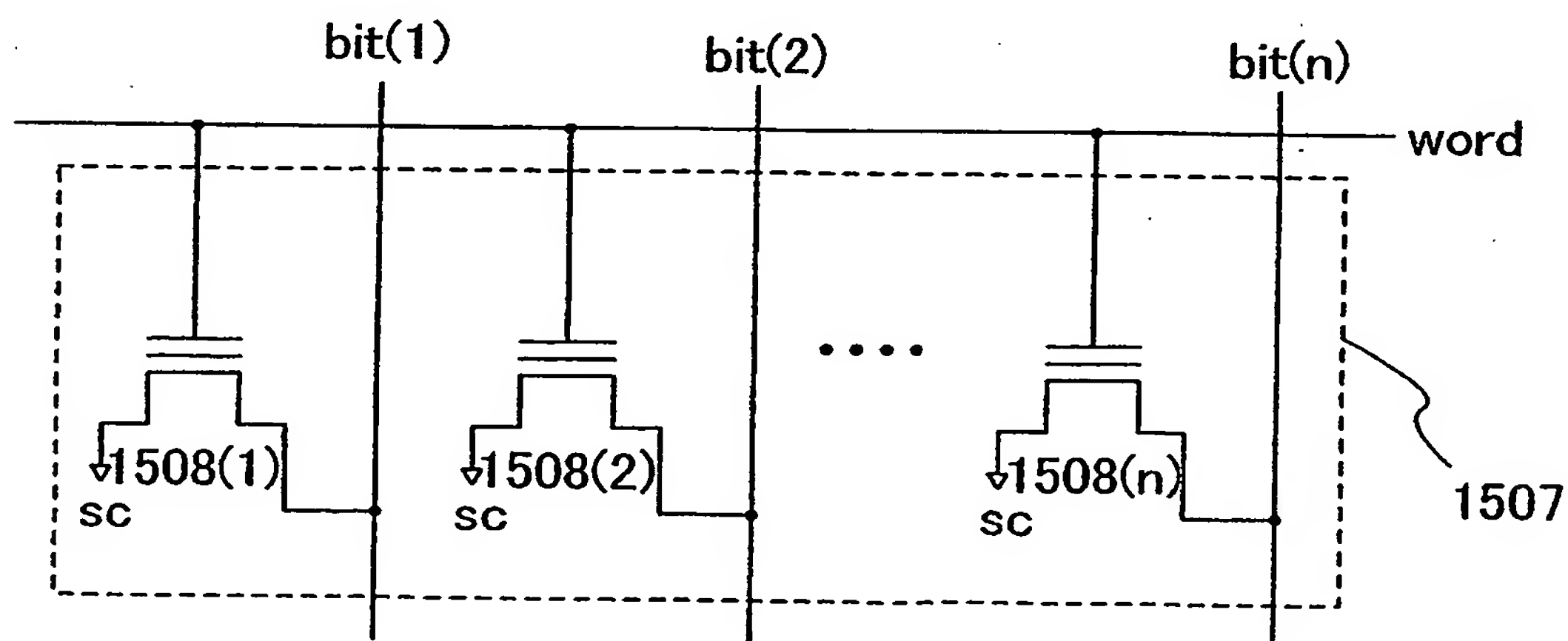


FIG. 21

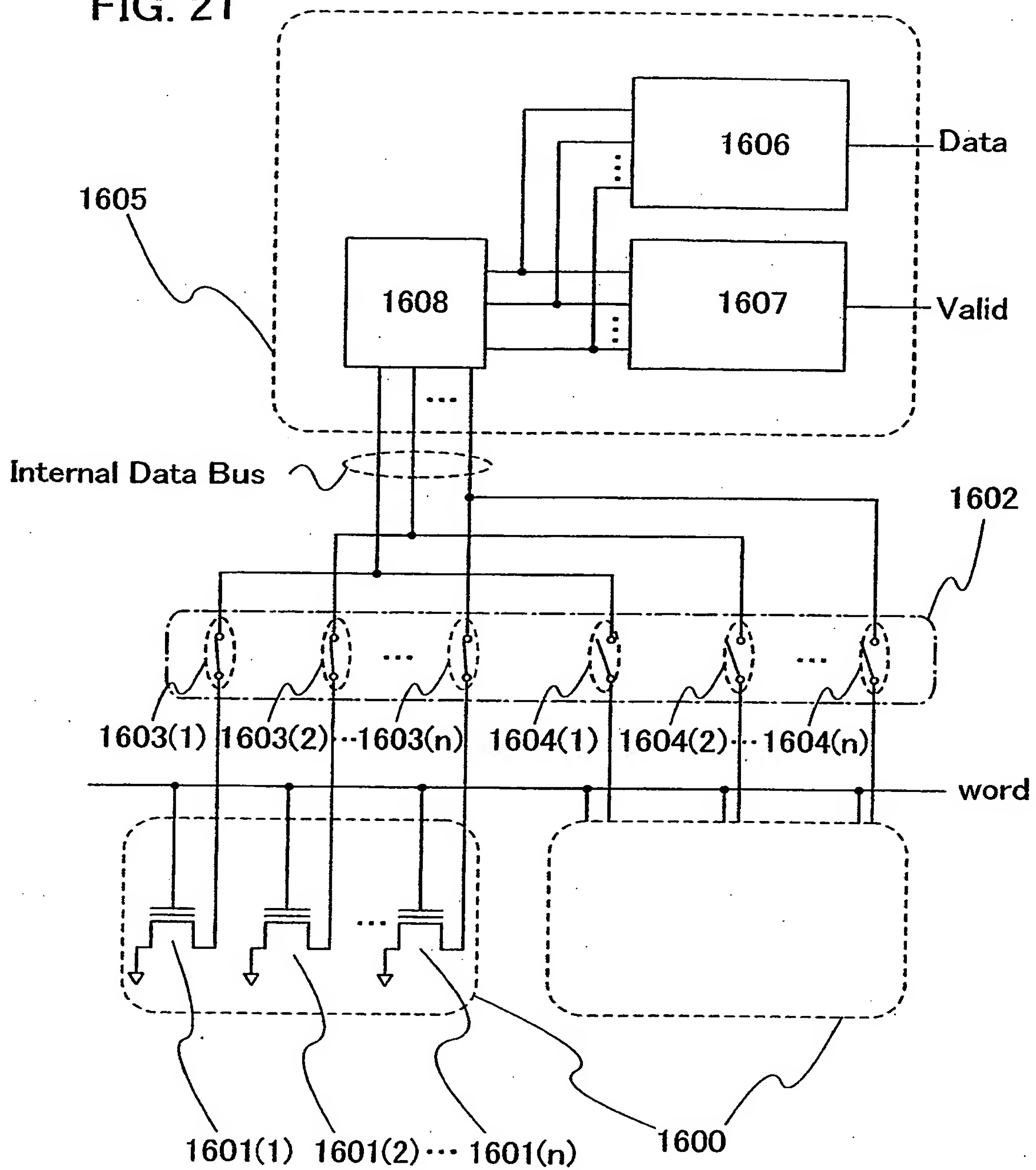


FIG. 22

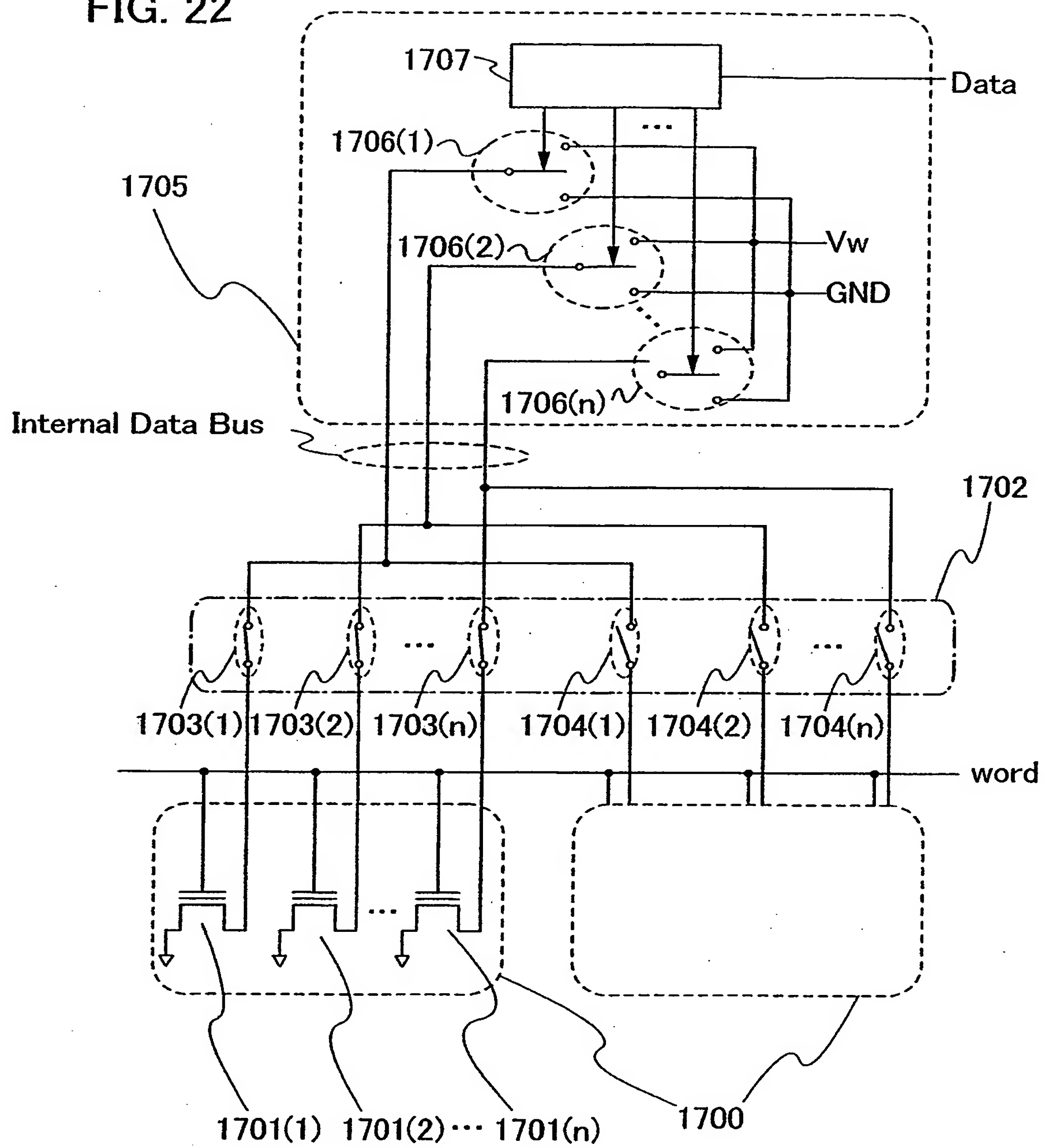


FIG. 23A

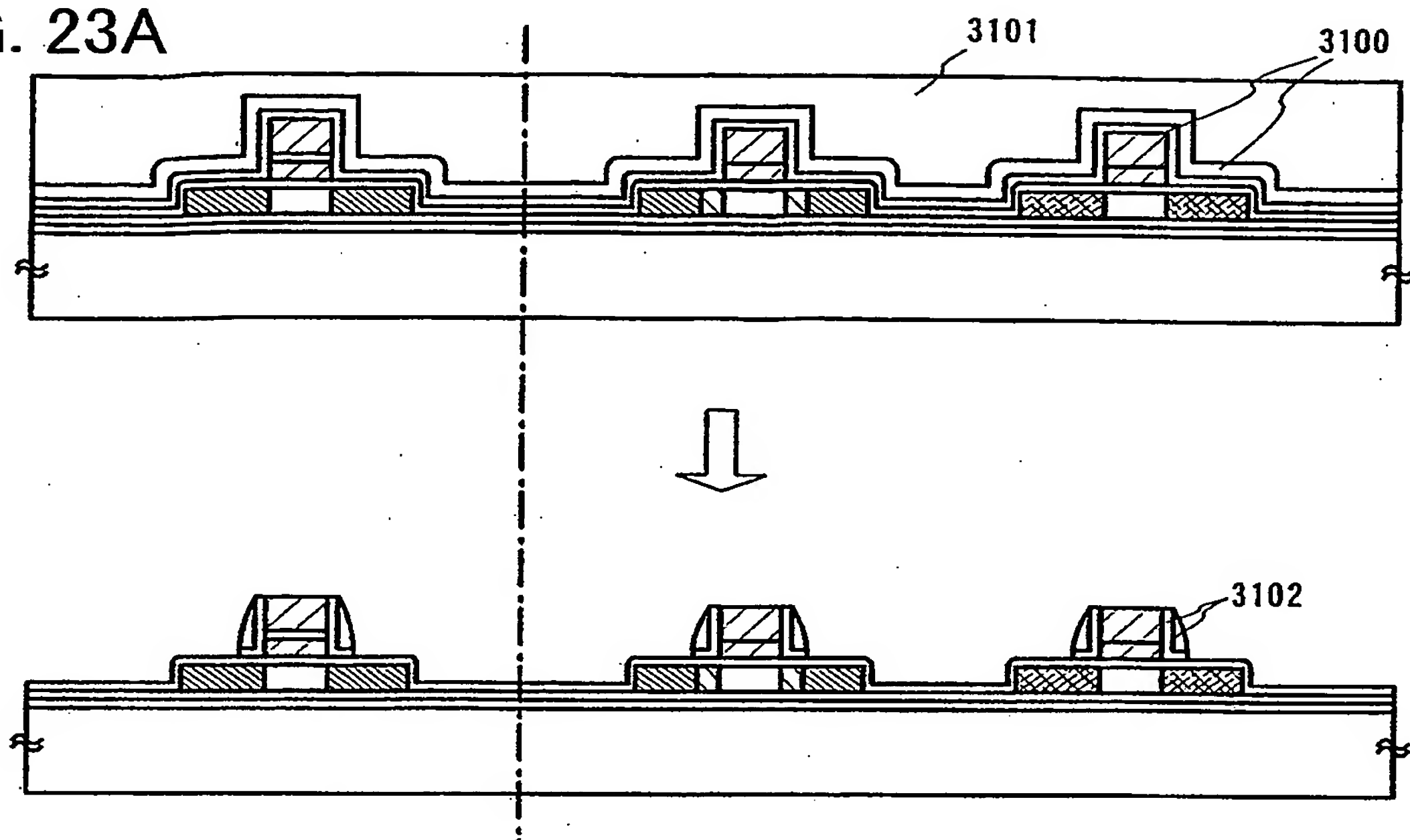
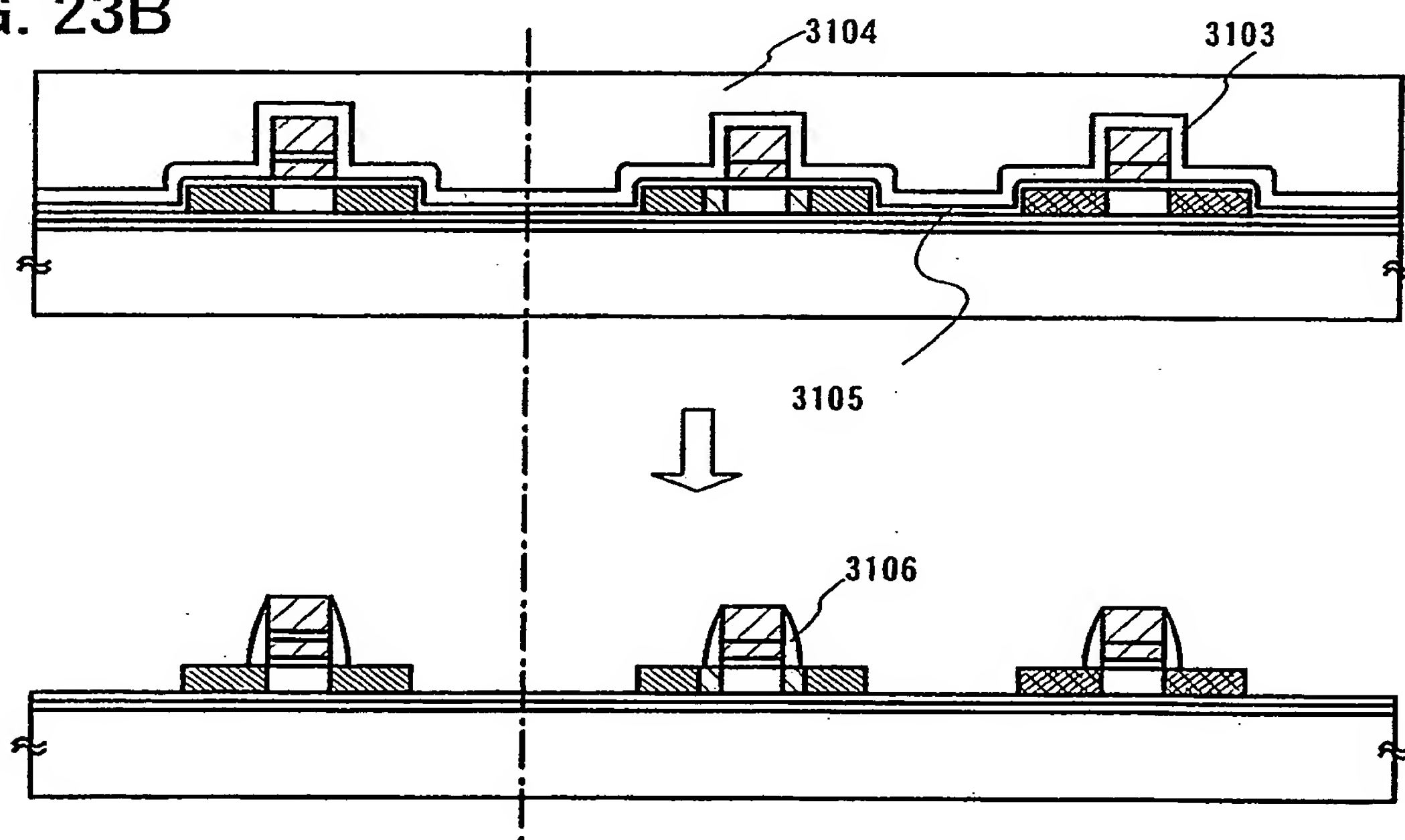


FIG. 23B



## EXPLANATION OF REFERENCE

100: substrate, 101: write circuit, 102: read circuit, 103: row decoder, 104: column decoder, 105: selector, 106: memory cell array, 107: memory cell, 108: first memory element, 109: second memory element, 150: substrate, 151: write circuit, 152: read circuit, 153: row decoder, 154: column decoder, 155: selector, 156: memory cell array, 157: memory cell, 158: first memory element, 159: second memory element, 160: third memory element, 200: memory cell, 201: first memory element, 202: second memory element, 203: selector, 204: switch, 205: switch, 206: switch, 207: switch, 208: switch, 209: switch, 210: read circuit, 211: XOR gate, 212: resistor, 213: resistor, 250: memory cell, 251: first memory element, 252: second memory element, 253: third memory element, 254: selector, 255: switch, 256: switch, 257: switch, 258: switch, 259: switch, 260: switch, 261: read circuit, 262: converting circuit, 263: determining circuit, 264: read circuit, 800: MNOS memory element, 801: gate electrode, 802: nitride film, 803: oxide film, 804: substrate, 805: source region, 806: drain region, 810: MONOS memory element, 811: gate electrode, 812: oxide film, 813: nitride film, 814: oxide film, 815: substrate, 816: source region, 817: drain region, 900: memory element, 901: gate electrode, 902: microcrystalline Si layer, 903: substrate, 904: source region, 905: drain region, 1001: IDF chip, 1002: bag, 1003: IDF chip, 1004: passport, 1005: IDF chip, 1006: driver's license, 1101: IDF chip, 1102, paper money, 1103: thin film transistor, 1104: source region, 1105: channel forming region, 1106: drain region, 1200: IC card, 1201: incorporated memory, 1210: ID tag, 1211: incorporated memory, 1220: product, 1221: protective film, 1222: ID chip, 1230: housing, 1231: ID chip, 1240: tag, 1241: ID chip, 1250: book, 1251: protective film, 1252: ID chip, 1260: paper money, 1261: ID chip, 1270: shoe, 1271: protective film, 1272: ID chip, 1300: memory cell, 1301: first memory element, 1302: second memory element, 1303: selector, 1304: switch, 1305: switch, 1306: switch, 1307: switch, 1308: switch, 1309: switch, 1310: write circuit, 1311:



switch, 1312: switch, 1313: inverter, 1350: memory cell, 1351: first memory element, 1352: second memory element, 1353: third memory element, 1354: selector, 1355: switch, 1356: switch, 1357: switch, 1358: switch, 1359: switch, 1360: switch, 1361: write circuit, 1362: switch, 1363: switch, 1364: switch, 1365: converting circuit, 1401: ID chip, 1402: antenna, 1403: RF circuit, 1404: power source/ clock signal/ reset signal generating circuit, 1405: data demodulating/modulating circuit, 1406: controlling circuit, 1407: memory, 1500: substrate, 1501: write circuit, 1502: read circuit, 1503: row decoder, 1504: column decoder, 1505: selector, 1506: memory cell array, 1507: memory cell, 1508: memory element, 1600: memory cell, 1601: memory element, 1602: selector, 1603: switch, 1604: switch, 1605: read circuit, 1606: converting circuit, 1607: determining circuit, 1608: an internal data reading circuit, 1700: memory cell, 1701: memory element, 1702: selector, 1703: switch, 1704: switch, 1705: write circuit, 1706: switch, 1707: converting circuit, 2301: IDF chip, 2302: label, 2304: IDF chip, 2305: bottle, 2306: label, 3000: insulating substrate, 3001: base film, 3002: base film, 3003: semiconductor layer, 3004: semiconductor layer, 3005: semiconductor layer, 3006: gate insulating film, 3007: conductive layer, 3008: conductive layer, 3009: conductive layer, 3010: gate insulating film, 3011: conductive layer, 3012: conductive layer, 3013: conductive layer, 3014: impurity region, 3015: impurity region, 3016: impurity region, 3017: impurity region, 3018: impurity region, 3019: impurity region, 3020: side wall, 3012: side wall, 3022: impurity region, 3023: impurity region, 3024: interlayer film, 3025: interlayer film, 3026: electrode, 3027: electrode, 3028: electrode, 3029: electrode, 3030: electrode, 3100: insulating film, 3101: resist, 3102: side wall, 3103: insulating film, 3104: resist, 3105: gate insulating film, 3106: side wall, 4000: peeling layer, 4001: interlayer insulating film, 4004: pad, 4005: pad, 4006: protective layer, 4007: groove, 4008: adhesive, 4009: support base.